

DS0141
Datasheet
PolarFire FPGA



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Contents

1	Revision History	1
1.1	Revision 1.0	1
2	PolarFire FPGA Datasheet	2
2.1	Introduction	2
2.2	References	2
2.3	Device Offering	2
2.4	Silicon Status	3
2.5	DC Characteristics	3
2.5.1	Absolute Maximum Rating	3
2.5.2	Recommended Operating Conditions	4
2.5.2.1	DC Characteristics Over Recommended Operating Conditions	5
2.5.2.2	Maximum Allowed Overshoot and Undershoot	6
2.5.2.3	Power-Supply Ramp Times	9
2.5.2.4	Hot Socketing	9
2.5.3	I/O	10
2.5.3.1	DC Input and Output Levels	10
2.5.3.2	Differential DC Input and Output Levels	12
2.5.3.3	Complementary Differential DC Input and Output Levels	13
2.5.3.4	HSIO On-Die Termination	14
2.5.3.5	GPIO On-Die Termination	15
2.5.3.6	LVDS	16
2.6	AC Switching Characteristics	17
2.6.1	I/O Standards Specifications	17
2.6.1.1	Input Delay Measurement Methodology	17
2.6.1.2	Output Delay Measurement Methodology	20
2.6.1.3	Input Buffer Speed	22
2.6.1.4	Output Buffer Speed	24
2.6.1.5	Maximum PHY Rate for Memory Interface IP	26
2.6.1.6	User I/O Switching Characteristics	26
2.6.1.7	I/O Digital Latency	30
2.6.1.8	I/O Digital Training Calibration	32
2.6.2	Clocking Specifications	34
2.6.2.1	Clocking	34
2.6.2.2	PLL	35
2.6.2.3	DLL	37
2.6.2.4	RC Oscillators	38
2.6.3	Fabric Specifications	39
2.6.3.1	Math Blocks	39
2.6.3.2	LSRAM Blocks	40
2.6.3.3	μSRAM Blocks	41
2.6.3.4	μPROM	42
2.6.4	Transceiver Switching Characteristics	42
2.6.4.1	Transceiver Performance	42
2.6.4.2	Transceiver Reference Clock Performance	43
2.6.4.3	Transceiver Reference Clock I/O Standards	43
2.6.4.4	Transceiver Interface Performance	44
2.6.4.5	Transmitter Performance	44
2.6.4.6	Receiver Performance	48
2.6.5	Transceiver Protocol Characteristics	50
2.6.5.1	PCI Express	50
2.6.5.2	10GbE (XAUI, RXAUI, 10GBASE-R, and 10GBASE-KR)	50
2.6.5.3	1GbE (SGMII, 1000BASE-T, 1000BASE-X, and QSGMII)	51
2.6.5.4	CPRI	51

2.6.5.5	JESD204B	52
2.6.6	Non-Volatile Characteristics	52
2.6.6.1	FPGA Programming Cycle and Retention	53
2.6.6.2	FPGA Programming Time	53
2.6.6.3	FPGA Bitstream Sizes	54
2.6.6.4	Digest Cycles	54
2.6.6.5	Digest Time	55
2.6.6.6	Zeroization Time	56
2.6.6.7	Verify Time	58
2.6.6.8	Secure NVM Performance	58
2.6.6.9	Secure NVM Programming Cycles	59
2.6.7	System Services	59
2.6.7.1	System Services Throughput Characteristics	59
2.6.8	User Crypto	61
2.6.8.1	TeraFire 5200B Switching Characteristics	61
2.6.8.2	TeraFire 5200B Throughput Characteristics	61
2.6.9	Fabric Macros	64
2.6.9.1	UJTAG Switching Characteristics	64
2.6.9.2	UJTAG_SEC Switching Characteristics	65
2.6.9.3	USPI Switching Characteristics	65
2.6.9.4	Tamper Detectors	66
2.6.9.5	System Controller Suspend Switching Characteristics	69
2.6.9.6	Dynamic Reconfiguration Interface	69
2.6.10	Power-Up to Functional Timing	71
2.6.10.1	LSRAM and μ SRAM Initialization Time	74
2.6.11	Dedicated Pins	75
2.6.11.1	JTAG Switching Characteristics	75
2.6.11.2	SPI Switching Characteristics	75
2.6.11.3	SmartDebug Probe Switching Characteristics	76
2.6.11.4	DEVRST_N Switching Characteristics	76
2.6.11.5	FF_EXIT Switching Characteristics	77
2.6.11.6	IO_CFG Switching Characteristics	77

Figures

Figure 1	Output Delay Measurement—Single-Ended Test Setup	21
Figure 2	Output Delay Measurement—Differential Test Setup	21
Figure 3	High-Temperature Retention (HTR) Curve	52
Figure 4	UJTAG Timing Diagram	65
Figure 5	USPI Switching Characteristics	66
Figure 6	ADC Switching Characteristics	67
Figure 7	ADC Switching Characteristics Timing Diagram	67
Figure 8	Write Transfer Without Wait States	69
Figure 9	Write Transfer With Wait States	70
Figure 10	Read Transfer Without Wait States	70
Figure 11	Read Transfer With Wait States	70
Figure 12	Cold-Boot Power-Up to Functional Times	73
Figure 13	Warm-Boot Power-Up to Functional Times	73

Tables

Table 1	PolarFire FPGA Device Options	2
Table 2	Silicon Status	3
Table 3	Absolute Maximum Ratings	3
Table 4	Recommended Operating Conditions	4
Table 5	DC Characteristics Over Recommended Operating Conditions	5
Table 6	Maximum Overshoot During Transitions for HSIO	6
Table 7	Maximum Undershoot During Transitions for HSIO	7
Table 8	Maximum Overshoot During Transitions for GPIO	7
Table 9	Maximum Allowed Undershoot During Transitions for GPIO	8
Table 10	Power-Supply Ramp Times	9
Table 11	DC Characteristics Over Recommended Operating Conditions	9
Table 12	DC Input and Output Levels	10
Table 13	Differential DC Input and Output Levels	12
Table 14	Complementary Differential DC Input and Output Levels	13
Table 15	On-Die Termination Calibration Accuracy Specifications for HSIO Bank	14
Table 16	On-Die Termination Calibration Accuracy Specifications for GPIO Bank	15
Table 17	GPIO 3.3 V LVDS DC Specifications	16
Table 18	GPIO 2.5 V LVDS DC Specifications	16
Table 19	GPIO 1.8 V LVDS Receiver DC Specifications	16
Table 20	Input Delay Measurement Methodology	17
Table 21	Output Delay Measurement Methodology	20
Table 22	HSIO Maximum Input Buffer Speed	22
Table 23	GPIO Maximum Input Buffer Speed	23
Table 24	HSIO Maximum Output Buffer Speed	24
Table 25	GPIO Maximum Output Buffer Speed	25
Table 26	Maximum PHY Rate for Memory Interfaces IP for HSIO Banks	26
Table 27	Maximum PHY Rate for Memory Interfaces IP for GPIO Banks	26
Table 28	I/O Digital Receive Single-Data Rate Switching Characteristics	27
Table 29	I/O Digital Receive Double-Data Rate Switching Characteristics	27
Table 30	I/O Digital Transmit Single-Data Rate Switching Characteristics	28
Table 31	I/O Digital Transmit Double-Data Rate Switching Characteristics	29
Table 32	I/O Digital Receive Double-Data Rate Latency Characteristics	30
Table 33	I/O Digital Transmit Double-Data Rate Latency Characteristics	31
Table 34	I/O Digital Double-Data Rate Calibration Timing	32
Table 35	I/O Digital Training Timing	33
Table 36	Global and Regional Clock Characteristics	34
Table 37	High-Speed I/O Clock Characteristics	34
Table 38	PLL Electrical Characteristics	35
Table 39	DLL Electrical Characteristics	37
Table 40	2 MHz RC Oscillator Electrical Characteristics	38
Table 41	160 MHz RC Oscillator Electrical Characteristics	38
Table 42	Math Block Performance Extended Commercial Range	39
Table 43	Math Block Performance Industrial Range	39
Table 44	LSRAM Performance Extended Commercial Temperature Range	40
Table 45	μSRAM Performance	41
Table 46	LSRAM Performance Industrial Temperature Range	41
Table 47	μPROM Performance	42
Table 48	PolarFire Transceiver and TXPLL Performance	42
Table 49	PolarFire Transceiver Reference Clock AC Requirements	43
Table 50	Transceiver Differential Reference Clock I/O Standards	43
Table 51	Transceiver Single-Ended Reference Clock I/O Standards	44
Table 52	Transceiver Reference Clock Input Termination	44
Table 53	PolarFire Transceiver User Interface Clocks	44
Table 54	PolarFire Transceiver Transmitter Characteristics	46

Table 55	PolarFire Transceiver Receiver Characteristics	48
Table 56	PCI Express	50
Table 57	10GbE (XAUI, RXAUI, 10GBASE-R, and 10GBASE-KR)	50
Table 58	1GbE (SGMII, 1000BASE-T, 1000BASE-X, and QSGMII)	51
Table 59	CPRI	51
Table 60	JESD204B	52
Table 61	FPGA Programming Cycles Vs Retention Characteristics	53
Table 62	Master SPI Programming Time (IAP)	53
Table 63	Slave SPI Programming Time	53
Table 64	JTAG Programming Time	53
Table 65	Bitstream Sizes	54
Table 66	Maximum Number of Digest Cycles	54
Table 67	FPGA Programming Cycles Lifetime Factor	54
Table 68	Digest Times	55
Table 69	Zeroization Times for MPF100T, TL, TS, TLS Devices	56
Table 70	Zeroization Times for MPF200T, TL, TS, TLS Devices	56
Table 71	Zeroization Times for MPF300T, TL, TS, TLS Devices	57
Table 72	Zeroization Times for MPF500T, TL, TS, TLS Devices	57
Table 73	Standalone Fabric Verify Times	58
Table 74	Verify Time By Programming Hardware	58
Table 75	sNVM Read/Write Characteristics	58
Table 76	sNVM Programming Cycles Vs Retention Characteristics	59
Table 77	System Services Throughput Characteristics	59
Table 78	TeraFire F5200B Switching Characteristics	61
Table 79	TeraFire F5200B Throughput Characteristics	61
Table 80	UJTAG Performance Characteristics	64
Table 81	UJTAG Security Performance Characteristics	65
Table 82	SPI Macro Interface Timing Characteristics	65
Table 83	ADC Conversion Rate	66
Table 84	Temperature and Voltage Sensor Electrical Characteristics	67
Table 85	Tamper Macro Timing Characteristics—Flags and Clearing	67
Table 86	Tamper Macro Response Timing Characteristics	68
Table 87	System Controller Suspend Entry and Exit Characteristics	69
Table 88	Dynamic Reconfiguration Interface Timing Characteristics	69
Table 89	Power-Up to Functional Timing	71
Table 90	Ram Initialization Characteristics	74
Table 91	JTAG Electrical Characteristics	75
Table 92	SPI Electrical Characteristics	75
Table 93	SmartDebug Probe Performance Characteristics	76
Table 94	DEVRST_N Electrical Characteristics	76
Table 95	FF_EXIT Electrical Characteristics	77
Table 96	IO_CFG Electrical Characteristics	77

1 Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

1.1 Revision 1.0

Revision 1.0 is the first publication of this document.

2 PolarFire FPGA Datasheet

2.1 Introduction

This datasheet describes PolarFire™ FPGA device characteristics with industrial temperature range (–40 °C to 100 °C T_J) and extended commercial temperature range (0 °C to 100 °C T_J). The devices are provided with a standard speed grade (STD) and a –1 speed grade with higher performance. The FPGA core supply V_{DD} can operate at 1.0 V for lower-power or 1.05 V for higher performance. Similarly, the transceiver core supply V_{DDA} can also operate at 1.0 V or 1.05 V. Users select the core operating voltage while creating the project.

2.2 References

The following documents are recommended references:

- [PO0137: PolarFire FPGA Product Overview](#)
- [UG0722: PolarFire FPGA Packaging and Pin Descriptions Users Guide](#)
- [UG0726: PolarFire FPGA Board Design User Guide](#)
- [UG0686: PolarFire FPGA User I/O User Guide](#)
- [UG0680: PolarFire FPGA Fabric User Guide](#)
- [UG0714: PolarFire FPGA Programming User Guide](#)
- [UG0684: PolarFire FPGA Clocking Resources User Guide](#)
- [UG0687: PolarFire FPGA 1G Ethernet Solutions User Guide](#)
- [UG0727: PolarFire FPGA 10G Ethernet Solutions User Guide](#)
- [UG0748: PolarFire FPGA Low Power User Guide](#)
- [UG0676: PolarFire FPGA DDR Memory Controller User Guide](#)
- [UG0743: PolarFire FPGA Debugging User Guide](#)
- [UG0725: PolarFire FPGA Device Power-Up and Resets User Guide](#)
- [UG0677: PolarFire FPGA Transceiver User Guide](#)
- [UG0685: PolarFire FPGA PCI Express User Guide](#)
- [UG0753: PolarFire FPGA Security User Guide \(to be released\)](#)
- [UG0752: PolarFire FPGA Power Estimator User Guide](#)

Note: For more information about PolarFire static and dynamic power data, see the [PolarFire Power Estimator Spreadsheet](#).

2.3 Device Offering

Table 1 • PolarFire FPGA Device Options

Device Options	Extended Commercial 0 °C - 100 °C	Industrial –40 °C - 100 °C	STD	–1	Transceivers T	Lower Static Power “L”	Data Security “S”
MPF300T	Yes	Yes	Yes	Yes	Yes		
MPF300TL	Yes	Yes	Yes		Yes	Yes	
MPF300TS		Yes	Yes	Yes	Yes		Yes
MPF300TLS		Yes	Yes		Yes	Yes	Yes

2.4 Silicon Status

There are three silicon status levels:

- **Advanced**—contains initial estimated information based on simulations
- **Preliminary**—contains information based on simulation and/or initial characterization
- **Production**—contains the final production silicon data

The following table shows the status of the PolarFire FPGA device.

Table 2 • Silicon Status

Device	Status
MPF100T, TL, TS, TLS	Advanced
MPF200T, TL, TS, TLS	Advanced
MPF300T, TL, TS, TLS	Advanced
MPF500T, TL, TS, TLS	Advanced

2.5 DC Characteristics

2.5.1 Absolute Maximum Rating

Table 3 • Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
Core power supply	V_{DD}	-0.5	1.13	V
Transceiver core power supply	V_{DDA}	-0.5	1.13	V
Must connect to 1.8 V	V_{DD18}	-0.5	2.0	V
Must connect to 2.5 V	V_{DD25}	-0.5	2.7	V
Must connect to 2.5 V	V_{DDA25}	-0.5	2.7	V
GPIO auxiliary power supply for I/O bank 2	V_{DDAUX2}	-0.5	3.6	V
GPIO auxiliary power supply for I/O bank 4	V_{DDAUX4}	-0.5	3.6	V
GPIO auxiliary power supply for I/O bank 5	V_{DDAUX5}	-0.5	3.6	V
Transceiver reference clock input buffer power supply	$V_{DD_XCVR_CLK}$	-0.5	3.6	V
Transceiver reference clock input buffer comparator voltage reference	$XCVR_{VREF}$	-0.5	3.6	V
DC I/O supply voltage for HSIO	V_{DDIx}	-0.5	2.0	V
DC I/O supply voltage for GPIO	V_{DDIx}	-0.5	3.6	V
DC I/O supply voltage for JTAG	V_{DDI3}	-0.5	3.6	V
DC I/O supply voltage for SPI	V_{DDI3}	-0.5	3.6	V
Receiver absolute input voltage	Transceiver V_{IN}	-0.5	1.26	V
Reference clock absolute input voltage	Transceiver REFCLK V_{IN}	-0.5	3.6	V
Storage temperature (ambient) ¹	T_{STG}	-65	150	°C
Junction temperature	T_J	-55	135	°C
Maximum soldering temperature RoHS	$T_{SOLROHS}$		260	°C
Maximum soldering temperature leaded	T_{SOLPB}		220	°C
Maximum DC input voltage on GPIO	V_{IN}	-0.5	3.8	V

Table 3 • Absolute Maximum Ratings (continued)

Parameter	Symbol	Min	Max	Unit
Maximum DC input voltage on HSIO	V_{IN}	-0.5	2.2	V

- See Table 61, page 53 for retention time vs. temperature. The total time used in calculating the device retention includes storage time and the device stored temperature.

2.5.2 Recommended Operating Conditions

The following table lists the recommended operating conditions.

Table 4 • Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
FPGA core supply at 1.0 V mode ¹	V_{DD}	0.97	1.00	1.03	V
FPGA core supply at 1.05 V mode ¹	V_{DD}	1.02	1.05	1.08	V
Transceiver core supply at 1.0 V mode ¹	V_{DDA}	0.97	1.00	1.03	V
Transceiver core supply at 1.05 V mode ¹	V_{DDA}	1.02	1.05	1.08	V
Must connect to 1.8 V	V_{DD18}	1.71	1.80	1.89	V
FPGA core and core PLL high-voltage supply	V_{DD25}	2.425	2.50	2.575	V
Transceiver PLL high-voltage supply	V_{DDA25}	2.425	2.50	2.575	V
HSIO allow 1.2 V, 1.5 V, and 1.8 V nominal options	V_{DDIx}	1.14	Various	1.89	V
GPIO allow 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V nominal options ²	V_{DDIx}	1.14	Various	3.465	V
Bank 3 dedicated I/O buffers allow 1.8 V, 2.5 V, and 3.3 V nominal options (GPIO) ²	V_{DDI3}	1.71	Various	3.465	V
GPIO with $V_{DDI2} = 3.3$ V nominal ²	V_{DDAUX2}	3.135	3.3	3.465	V
GPIO with $V_{DDI4} = 3.3$ V nominal ²	V_{DDAUX4}	3.135	3.3	3.465	V
GPIO with $V_{DDI5} = 3.3$ V nominal ²	V_{DDAUX5}	3.135	3.3	3.465	V
GPIO with $V_{DDI2} = 2.5$ V nominal or lower ²	V_{DDAUX2}	2.375	2.5	2.625	V
GPIO with $V_{DDI2} = 2.5$ V nominal or lower ²	V_{DDAUX4}	2.375	2.5	2.625	V
GPIO with $V_{DDI2} = 2.5$ V nominal or lower ²	V_{DDAUX5}	2.375	2.5	2.625	V
Transceiver reference clock supply -3.3 V nominal	$V_{DD_XCVR_CLK}$	3.135	3.3	3.465	V
Transceiver reference clock supply -2.5 V nominal	$V_{DD_XCVR_CLK}$	2.375	2.5	2.625	V
Global V_{REF} for transceiver reference clocks ³	$XCVR_{VREF}$	Ground		$V_{DD_XCVR_CLK}$	V
Extended commercial temperature range	T_J	0		100	°C
Industrial temperature range		-40		100	°C
Extended commercial programming temperature range	T_{PRG}	0		100	°C
Industrial programming temperature range		-40		100	°C

- V_{DD} and V_{DDA} can independently operate at 1.0 V or 1.05 V nominal. These are not dynamically adjustable.
- For GPIO buffers where I/O bank is designated as bank #, if V_{DDIx} is 2.5 V nominal or 3.3 V nominal, V_{DDAUXx} must be connected to the V_{DDIx} supply for that bank. If V_{DDIx} for a given GPIO bank is < 2.5 V nominal, V_{DDAUXx} per I/O bank must be powered at 2.5 V nominal.
- $XCVR_{VREF}$ globally sets the reference voltage of the transceiver's single-ended reference clock input buffers. It is typically near $V_{DD_XCVR_CLK}/2$ V but is allowed in the specified range.

2.5.2.1 DC Characteristics Over Recommended Operating Conditions

The following table lists the DC characteristics over recommended operating conditions.

Table 5 • DC Characteristics Over Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit	Condition
Input pin capacitance ¹	C_{IN} (dedicated GPIO)		5.6	pf	
	C_{IN} (GPIO)		5.6	pf	
	C_{IN} (HSIO)		2.8	pf	
Input or output leakage current per pin	I_L (GPIO)		0.1	μA	I/O disabled, high - Z
	I_L (HSIO)		0.1	μA	I/O disabled, high - Z
Input rise time (10%–90% of V_{DDIX}) ^{2, 3, 4}	T_{RISE}	0.66	2.64	ns	$V_{DDIX} = 3.3\text{ V}$
Input rise time (10%–90% of V_{DDIX}) ^{2, 3, 4}		0.50	2.00	ns	$V_{DDIX} = 2.5\text{ V}$
Input rise time (10%–90% of V_{DDIX}) ^{2, 3, 4}		0.36	1.44	ns	$V_{DDIX} = 1.8\text{ V}$
Input rise time (10%–90% of V_{DDIX}) ^{2, 3, 4}		0.30	1.20	ns	$V_{DDIX} = 1.5\text{ V}$
Input rise time (10%–90% of V_{DDIX}) ^{2, 3, 4}		0.24	0.96	ns	$V_{DDIX} = 1.2\text{ V}$
Input fall time (90%–10% of V_{DDIX}) ^{2, 3, 4}	T_{FALL}	0.66	2.64	ns	$V_{DDIX} = 3.3\text{ V}$
Input fall time (90%–10% of V_{DDIX}) ^{2, 3, 4}		0.50	2.00	ns	$V_{DDIX} = 2.5\text{ V}$
Input fall time (90%–10% of V_{DDIX}) ^{2, 3, 4}		0.36	1.44	ns	$V_{DDIX} = 1.8\text{ V}$
Input fall time (90%–10% of V_{DDIX}) ^{2, 3, 4}		0.30	1.20	ns	$V_{DDIX} = 1.5\text{ V}$
Input fall time (90%–10% of V_{DDIX}) ^{2, 3, 4}		0.24	0.96	ns	$V_{DDIX} = 1.2\text{ V}$
Pad pull-up when $V_{IN} = 0^5$	I_{PU}	150	216	μA	$V_{DDIX} = 3.3\text{ V}$
Pad pull-up when $V_{IN} = 0^5$		111	161	μA	$V_{DDIX} = 2.5\text{ V}$
Pad pull-up when $V_{IN} = 0$		72	111	μA	$V_{DDIX} = 1.8\text{ V}$
Pad pull-up when $V_{IN} = 0$		51	88	μA	$V_{DDIX} = 1.5\text{ V}$
Pad pull-up when $V_{IN} = 0^6$		29	73	μA	$V_{DDIX} = 1.35\text{ V}$
Pad pull-up when $V_{IN} = 0$		16	46	μA	$V_{DDIX} = 1.2\text{ V}$
Pad pull-up when $V_{IN} = 0^6$	I_{PD}	8	25	μA	$V_{DDIX} = 1.1\text{ V}$
Pad pull-down when $V_{IN} = 3.3\text{ V}^5$		65	187	μA	$V_{DDIX} = 3.3\text{ V}$
Pad pull-down when $V_{IN} = 2.5\text{ V}^5$		63	160	μA	$V_{DDIX} = 2.5\text{ V}$
Pad pull-down when $V_{IN} = 1.8\text{ V}$		60	117	μA	$V_{DDIX} = 1.8\text{ V}$
Pad pull-down when $V_{IN} = 1.5\text{ V}$		57	95	μA	$V_{DDIX} = 1.5\text{ V}$
Pad pull-down when $V_{IN} = 1.35\text{ V}^6$		52	86	μA	$V_{DDIX} = 1.35\text{ V}$
Pad pull-down when $V_{IN} = 1.2\text{ V}$		49	77	μA	$V_{DDIX} = 1.2\text{ V}$
Pad pull-down when $V_{IN} = 1.1\text{ V}^6$		45	71	μA	$V_{DDIX} = 1.1\text{ V}$

1. Represents the die input capacitance at the pad not the package.
2. Voltage ramp must be monotonic.
3. Numbers based on rail-to-rail input signal swing and minimum 1 V/ns and maximum 4 V/ns. These are to be used for input delay measurement consistency.
4. I/O signal standards with smaller than rail-to-rail input swings can use a nominal value of 200 ps 20–80% of swing and maximum value of 500 ps 20–80% of swing.
5. GPIO only.
6. HSIO only.

2.5.2.2 Maximum Allowed Overshoot and Undershoot

During transitions, input signals may overshoot and undershoot the voltage shown in the following table. Input currents must be limited to less than 100 mA per latch-up specifications.

The maximum overshoot duration is specified as a high-time percentage over the lifetime of the device. A DC signal is equivalent to 100% of the duty-cycle.

The following table shows the maximum overshoot duration for HSIO.

Table 6 • Maximum Overshoot During Transitions for HSIO

Parameter	Symbol	Overshoot Duration as % @ $T_J = 100\text{ }^{\circ}\text{C}$	Condition (V)
AC input voltage	V_{IN}	100	1.8
		100	1.85
		100	1.9
		100	1.95
		100	2
		100	2.05
		100	2.1
		100	2.15
		100	2.2
		90	2.25
		30	2.3
		7.5	2.35
		1.9	2.4

The following table shows the maximum undershoot duration for HSIO.

Table 7 • Maximum Undershoot During Transitions for HSIO

Parameter	Symbol	Undershoot ¹ Duration as % @ T _J = 100 °C	Condition (V)
AC input voltage	V _{IN}	100	-0.05
		100	-0.1
		100	-0.15
		100	-0.2
		100	-0.25
		100	-0.3
		100	-0.35
		100	-0.4
		44	-0.45
		14	-0.5
		4.8	-0.55
		1.6	-0.6

1. Undershoot level is with reference to 1.8 V V_{DDI}.

The following table shows the maximum overshoot duration for GPIO.

Table 8 • Maximum Overshoot During Transitions for GPIO

Parameter	Symbol	Overshoot Duration as % @ T _J = 100 C	Condition (V)
AC input voltage	V _{IN}	100	3.8
		100	3.85
		100	3.9
		100	3.95
		70	4
		50	4.05
		33	4.1
		22	4.15
		14	4.2
		9.8	4.25
		6.5	4.3
		4.4	4.35
		3	4.4
		2	4.45
		1.4	4.5
		0.9	4.55
		0.6	4.6

The following table shows the maximum undershoot duration for GPIO.

Table 9 • Maximum Allowed Undershoot During Transitions for GPIO

Parameter	Symbol	Undershoot ¹ Duration as % @ T _J = 100 °C	Condition (V)
AC input voltage	V _{IN}	100	–0.5
		100	–0.55
		100	–0.6
		100	–0.65
		100	–0.7
		100	–0.75
		100	–0.8
		100	–0.85
		100	–0.9
		100	–0.95
		100	–1
		100	–1.05
		100	–1.1
		100	–1.15
		100	–1.2
		69	–1.25
		45	–1.3

1. Undershoot level is with reference to 3.3 V V_{DDI}.

2.5.2.3 Power-Supply Ramp Times

The following table shows the power-up ramp times. All supplies must rise and fall monotonically. There are no power-supply sequencing requirements for PolarFire devices.

Note: Power-supply ramp must be monotonic.

Table 10 • Power-Supply Ramp Times

Parameter	Symbol	Min	Max	Unit
FPGA core supply	V_{DD}	0.2	100	ms
Transceiver core supply	V_{DDA}	0.2	100	ms
Must connect to 1.8 V supply	V_{DD18}	0.2	100	ms
Must connect to 2.5 V supply	V_{DD25}	0.2	100	ms
Must connect to 2.5 V supply	V_{DDA25}	0.2	100	ms
HSIO bank I/O power supplies	$V_{DDI[0,1,6,7]}$	0.2	100	ms
GPIO bank I/O power supplies	$V_{DDI[2,4,5]}$	0.2	100	ms
Bank 3 dedicated I/O buffers (GPIO)	V_{DDI3}	0.2	100	ms
GPIO bank auxiliary power supplies	$V_{DDAUX[2,4,5]}$	0.2	100	ms
Transceiver reference clock supply –3.3 V nominal	$V_{DD_XCVR_CLK}$	0.2	100	ms
Global V_{REF} for transceiver reference clocks	$XCVR_{VREF}$	0.2	100	ms

2.5.2.4 Hot Socketing

The following table lists the hot-socketing DC characteristics over recommended operating conditions.

Table 11 • DC Characteristics Over Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Current per transceiver Rx input pin (P or N single-ended) ^{1, 2}	$XCVR_{RX_HS}$			±4	mA	$V_{DDA} = 0\text{ V}$
Current per transceiver Tx output pin (P or N single-ended) ³	$XCVR_{TX_HS}$			±10	uA	$V_{DDA} = 0\text{ V}$
Current per transceiver reference clock input pin (P or N single-ended) ⁴	$XCVR_{REF_HS}$			±1	mA	$V_{DD_XCVR_CLK} = 0\text{ V}$
Current per GPIO pin (P or N single-ended) ⁵	I_{GPIO_HS}			±1	mA	$V_{DDIx} = 0\text{ V}$
Current per HSIO pin (P or N single-ended) ⁶						

1. Assumes that the device is powered-down, all supplies are grounded, AC coupled interface, and input pin pairs are driven by a CML driver at the maximum amplitude (1 V pk-pk) that is toggling at any rate with PRBS 2⁷ data.
2. Each P and N transceiver input has less than the specified maximum input current.
3. Each P and N transceiver output is connected to a 40 Ω resistor (50 Ω CML termination – 20% tolerance) to the maximum allowed output voltage ($V_{DDAmax} + 0.3\text{ V} = 1.4\text{ V}$) through an AC coupling capacitor with all PolarFire device supplies grounded. This shows the current for a worst-case DC coupled interface. As an AC coupled interface, the output signal will settle at ground and no socket current will be seen.
4. $V_{DD_XCVR_CLK}$ is powered down and the device is driven to $-0.5\text{ V} < V_{IN} < V_{DD_XCVR_CLK}$.
5. V_{DDIx} is powered down and the device is driven to $-0.5\text{ V} < V_{IN} < \text{GPIO } V_{DDImax}$.
6. Not supported.

2.5.3 I/O

This section describes:

- DC I/O levels
- differential and complementary differential DC I/O levels
- HSIO and GPIO on die termination specifications
- LVDS specifications

2.5.3.1 DC Input and Output Levels

The following table lists the DC I/O levels.

Table 12 • DC Input and Output Levels

I/O Standard	V _{DDI}			V _{IL}		V _{IH}		V _{OL}		V _{OH}		I _{OL} I _{OH}	
	Min	Typ	Max	Min	Max	Min	Max ¹	Min	Max	Min	Max	mA	mA
PCI ²	3.15	3.3	3.45	-0.3	0.3 × V _{DDI}	0.5 × V _{DDI}	3.45	0.1 × V _{DDI}	0.9 × V _{DDI}			1.5	0.5
LVTTL ³	3.15	3.3	3.45	-0.3	0.8	2	3.45	0.4	2.4				
LVC MOS33 ³	3.15	3.3	3.45	-0.3	0.8	2	3.45	0.4	V _{DDI} - 0.4				
LVC MOS25 ⁴	2.375	2.5	2.625	-0.3	0.7	1.7	2.625	0.4	V _{DDI} - 0.4				
LVC MOS18 ⁵	1.71	1.8	1.89	-0.3	0.35 × V _{DDI}	0.65 × V _{DDI}	1.89	0.45	V _{DDI} - 0.45				
LVC MOS15 ⁶	1.425	1.5	1.575	-0.3	0.35 × V _{DDI}	0.65 × V _{DDI}	1.575	0.25 × V _{DDI}	0.75 × V _{DDI}				
LVC MOS12 ⁷	1.14	1.2	1.26	-0.3	0.35 × V _{DDI}	0.65 × V _{DDI}	1.26	0.25 × V _{DDI}	0.75 × V _{DDI}				
SSTL25I ⁸	2.375	2.5	2.625	-0.3	V _{REF} - 0.15	V _{REF} + 0.15	2.625	V _{TT} - 0.608	V _{TT} + 0.608			8.1	8.1
SSTL25II ⁸	2.375	2.5	2.625	-0.3	V _{REF} - 0.15	V _{REF} + 0.15	2.625	V _{TT} - 0.810	V _{TT} + 0.810			16.2	16.2
SSTL18I ⁸	1.71	1.8	1.89	-0.3	V _{REF} - 0.125	V _{REF} + 0.125	1.89	V _{TT} - 0.603	V _{TT} + 0.603			6.7	6.7
SSTL18II ⁸	1.71	1.8	1.89	-0.3	V _{REF} - 0.125	V _{REF} + 0.125	1.89	V _{TT} - 0.603	V _{TT} + 0.603			13.4	13.4
SSTL15I ⁹	1.425	1.5	1.575	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.575	0.2 × V _{DDI}	0.8 × V _{DDI}			V _{OL} /40	(V _{DDI} - V _{OH})/40
SSTL15II ⁹	1.425	1.5	1.575	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.575	0.2 × V _{DDI}	0.8 × V _{DDI}			V _{OL} /34	(V _{DDI} - V _{OH})/34
SSTL135I ⁹	1.283	1.35	1.418	-0.3	V _{REF} - 0.09	V _{REF} + 0.09	1.418	0.2 × V _{DDI}	0.8 × V _{DDI}			V _{OL} /40	(V _{DDI} - V _{OH})/40
SSTL135II ⁹	1.283	1.35	1.418	-0.3	V _{REF} - 0.09	V _{REF} + 0.09	1.418	0.2 × V _{DDI}	0.8 × V _{DDI}			V _{OL} /34	(V _{DDI} - V _{OH})/34
HSTL15I	1.425	1.5	1.575	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.575	0.4	V _{DDI} - 0.4			8	8
HSTL15II	1.425	1.5	1.575	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.575	0.4	V _{DDI} - 0.4			16	16
HSTL135I ⁹	1.283	1.35	1.418	-0.3	V _{REF} - 0.09	V _{REF} + 0.09	1.418	0.2 × V _{DDI}	0.8 × V _{DDI}			V _{OL} /50	(V _{DDI} - V _{OH})/50
HSTL135II ⁹	1.283	1.35	1.418	-0.3	V _{REF} - 0.09	V _{REF} + 0.09	1.418	0.2 × V _{DDI}	0.8 × V _{DDI}			V _{OL} /25	(V _{DDI} - V _{OH})/25
HSTL12I ⁹	1.14	1.2	1.26	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.26	0.1 × V _{DDI}	0.9 × V _{DDI}			V _{OL} /50	(V _{DDI} - V _{OH})/50
HSTL12II ⁹	1.14	1.2	1.26	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.26	0.1 × V _{DDI}	0.9 × V _{DDI}			V _{OL} /25	(V _{DDI} - V _{OH})/25
HSUL18I ⁹	1.71	1.8	1.89	-0.3	0.3 × V _{DDI}	0.7 × V _{DDI}	1.89	0.1 × V _{DDI}	0.9 × V _{DDI}			V _{OL} /55	(V _{DDI} - V _{OH})/55
HSUL18II ⁹	1.71	1.8	1.89	-0.3	0.3 × V _{DDI}	0.7 × V _{DDI}	1.89	0.1 × V _{DDI}	0.9 × V _{DDI}			V _{OL} /25	(V _{DDI} - V _{OH})/25
HSUL12I ⁹	1.14	1.2	1.26	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.26	0.1 × V _{DDI}	0.9 × V _{DDI}			V _{OL} /40	(V _{DDI} - V _{OH})/40
POD12I ^{9, 10}	1.14	1.2	1.26	-0.3	V _{REF} - 0.08	V _{REF} + 0.08	1.26	0.5 × V _{DDI}				V _{OL} /48	(V _{DDI} - V _{OH})/48
POD12II ^{9, 10}	1.14	1.2	1.26	-0.3	V _{REF} - 0.08	V _{REF} + 0.08	1.26	0.5 × V _{DDI}				V _{OL} /34	(V _{DDI} - V _{OH})/34
LVSTL11I ⁹	1.045	1.1	1.155	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.155	0.1 × V _{DDI}	V _{DDI} /3			V _{OL} /40	(V _{DDI} - V _{OH})/80
LVSTL11II ⁹	1.045	1.1	1.155	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	1.155	0.1 × V _{DDI}	V _{DDI} /2.5			V _{OL} /40	(V _{DDI} - V _{OH})/60

1. GPIO V_{IH} max is 3.45 V with PCI clamp diode turned off regardless of mode, that is, over-voltage tolerant.
2. Drive strengths per PCI specification V/I curves.
3. Drive strengths of 2, 4, 8, 12, 16, 20 mA.
4. Drive strengths of 2, 4, 8, 12, 16, 20 mA.
5. Drive strengths of 2, 4, 6, 8, 12, 16 mA.
6. Drive strengths of 2, 4, 6, 8, 12 mA.
7. Drive strengths of 2, 4, 6, 8 mA.
8. For external stub-series resistance. This resistance is on-die for GPIO.
9. I_{OL}/I_{OH} Units for impedance standards in Amps (not mA).

10. VOH_MAX based on external pull-up termination (pseudo-open drain).

Note: 3.3 V and 2.5 V are only supported in GPIO banks.

2.5.3.2 Differential DC Input and Output Levels

Table 13 • Differential DC Input and Output Levels

I/O Standard	Bank Type	V_{ICM}^1			V_{ID}^2			V_{OCM}^3			V_{OD}^4		
		Min	Typ	Max ⁵	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max
LVDS33	GPIO	0.05	1.25	2.35	0.1	0.35	0.6	1.125	1.2	1.375	0.25	0.35	0.45
LVDS25	GPIO	0.05	1.25	2.35	0.1	0.35	0.6	1.125	1.2	1.375	0.25	0.35	0.45
LVDS18	GPIO	0.05	1.25	2.35	0.1	0.35	0.6						
LVDS18 ⁶	HSIO	0.05	1.25	1.65	0.1	0.35	0.6						
RSDS33	GPIO	0.05	1.25	2.35	0.1	0.2	0.6	1.19	1.2	1.31	0.17	0.2	0.23
RSDS25	GPIO	0.05	1.25	2.35	0.1	0.2	0.6	1.19	1.2	1.31	0.17	0.2	0.23
RSDS18 ⁷	HSIO	0.05	1.25	1.65	0.1	0.2	0.6						
MiniLVDS33	GPIO	0.05	1.25	2.35	0.1	0.3	0.6	1.125	1.2	2.375	0.3	0.4	0.6
MiniLVDS25	GPIO	0.05	1.25	2.35	0.1	0.3	0.6	1.125	1.2	2.375	0.3	0.4	0.6
MiniLVDS18 ⁷	HSIO	0.05	1.25	1.65	0.1	0.3	0.6						
SubLVDS33	GPIO	0.05	0.9	2.35	0.1	0.15	0.3	0.8	0.9	1	0.1	0.15	0.3
SubLVDS25	GPIO	0.05	0.9	2.35	0.1	0.15	0.3	0.8	0.9	1	0.1	0.15	0.3
SubLVDS18 ⁷	HSIO	0.05	0.9	1.65	0.1	0.15	0.3						
PPDS33	GPIO	0.05	0.8	2.35	0.1	0.2	0.6	0.5	0.8	1.4	0.17	0.2	0.23
PPDS25	GPIO	0.05	0.8	2.35	0.1	0.2	0.6	0.5	0.8	1.4	0.17	0.2	0.23
PPDS18 ⁷	HSIO	0.05	0.8	1.65	0.1	0.2	0.6						
SLVS33 ⁸	GPIO	0.05	0.2	2.35	0.1	0.2	0.3						
SLVS25 ⁸	GPIO	0.05	0.2	2.35	0.1	0.2	0.3						
SLVS18 ⁷	HSIO	0.05	0.2	1.65	0.1	0.2	0.3						
SLVSE15 ⁹	GPIO, HSIO							0.1	0.2	0.3	0.12	0.135	0.15
HCSL33 ⁸	GPIO	0.05	0.35	2.35	0.1	0.55	1.1						
HCSL25 ⁸	GPIO	0.05	0.35	2.35	0.1	0.55	1.1						
HCSL18 ⁷	HSIO	0.05	0.35	1.65	0.1	0.55	1.1						
BUSLVDSE25 ⁹	GPIO	0.05	1.25	2.35	0.05	0.1	V_{DDIn}	1.15	1.25	1.31	0.24	0.262	0.272
MLVDSE25 ⁹	GPIO	0.05	1.25	2.35	0.05	0.35	2.4	1.15	1.25	1.31	0.396	0.442	0.453
LVPECL33 ⁹	GPIO	0.05	1.65	2.35	0.05	0.8	2.4	1.51	1.65	1.74	0.664	0.722	0.755
LVPECLE33 ⁹	GPIO	0.05	1.65	2.35	0.05	0.8	2.4	1.51	1.65	1.74	0.664	0.722	0.755
MIPIE25 ⁹	GPIO	0.05	0.2	2.35	0.05	0.2	0.3	0.15	0.25	0.35	0.1	0.22	0.3
MIPI12 (high-speed)	GPIO	0.05	0.2	2.35	0.05	0.2	0.3						

1. V_{ICM} is the input common mode.
2. V_{ID} is the input differential voltage.
3. V_{OCM} is the output common mode voltage.
4. V_{OD} is the output differential voltage.
5. V_{ICM} must be less than $V_{DDI} - .3$ V.
6. HSIO receiver only, for AC transient purposes, V_{ICM} cannot exceed 0.95 V.
7. HSIO receiver only.
8. GPIO receiver only.
9. Emulated output only.

2.5.3.3 Complementary Differential DC Input and Output Levels

Table 14 • Complementary Differential DC Input and Output Levels

I/O Standard	V _{DDI}			V _{ICM} ¹			V _{ID} ²		V _{OL} ³		V _{OH} ³	I _{OL}	I _{OH}
	Min	Typ	Max	Min	Typ	Max	Min	Max	Min	Max	Min	mA, Max	mA, Min
SSTL25_DI	2.375	2.5	2.625	1.164	1.250	1.339	0.1		V _{TT} - 0.608	V _{TT} + 0.608		8.1	8.1
SSTL25_DII	2.375	2.5	2.625	1.164	1.250	1.339	0.1		V _{TT} - 0.810	V _{TT} + 0.810		16.2	16.2
SSTL18_DI	1.71	1.8	1.89	0.838	0.900	0.964	0.1		V _{TT} - 0.603	V _{TT} + 0.603		6.7	6.7
SSTL18_DII	1.71	1.8	1.89	0.838	0.900	0.964	0.1		V _{TT} - 0.603	V _{TT} + 0.603		13.4	13.4
SSTL15_DI ⁴	1.425	1.5	1.575	0.698	0.750	0.803	0.1		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /40	(V _{DDI} - V _{OH})/40	
SSTL15_DII ⁴	1.425	1.5	1.575	0.698	0.750	0.803	0.1		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /34	(V _{DDI} - V _{OH})/34	
SSTL135_DI ⁴	1.283	1.35	1.418	0.629	0.675	0.723	0.1		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /40	(V _{DDI} - V _{OH})/40	
SSTL135_DII ⁴	1.283	1.35	1.418	0.629	0.675	0.723	0.1		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /34	(V _{DDI} - V _{OH})/34	
HSTL15_DI	1.425	1.5	1.575	0.698	0.750	0.803	0.1		0.4	V _{DDI} - 0.4		8	8
HSTL15_DII	1.425	1.5	1.575	0.698	0.750	0.803	0.1		0.4	V _{DDI} - 0.4		16	16
HSTL135_DI ⁴	1.283	1.35	1.418	0.629	0.675	0.723	0.1		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /50	(V _{DDI} - V _{OH})/50	
HSTL135_DII ⁴	1.283	1.35	1.418	0.629	0.675	0.723	0.1		0.2 × V _{DDI}	0.8 × V _{DDI}	V _{OL} /25	(V _{DDI} - V _{OH})/25	
HSTL12_DI ⁴	1.14	1.2	1.26	0.559	0.600	0.643	0.1		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /50	(V _{DDI} - V _{OH})/50	
HSUL18_DI ⁴	1.71	1.8	1.89	0.838	0.900	0.964	0.1		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /55	(V _{DDI} - V _{OH})/55	
HSUL18_DII ⁴	1.71	1.8	1.89	0.838	0.900	0.964	0.1		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /25	(V _{DDI} - V _{OH})/25	
HSUL12_DI ⁴	1.14	1.2	1.26	0.559	0.600	0.643	0.1		0.1 × V _{DDI}	0.9 × V _{DDI}	V _{OL} /40	(V _{DDI} - V _{OH})/40	
POD12_DI ^{4, 5}	1.14	1.2	1.26	0.787	0.840	0.895	0.1		0.5 × V _{DDI}		V _{OL} /48	(V _{DDI} - V _{OH})/48	
POD12_DII ^{4, 5}	1.14	1.2	1.26	0.787	0.840	0.895	0.1		0.5 × V _{DDI}		V _{OL} /34	(V _{DDI} - V _{OH})/34	
LVSTL11_DI ⁴	1.045	1.1	1.155	0.172	0.183	0.194	0.1		0.1 × V _{DDI}	V _{DDI} /3	V _{OL} /40	(V _{DDI} - V _{OH})/80	
LVSTL11_DII ⁴	1.045	1.1	1.155	0.207	0.220	0.233	0.1		0.1 × V _{DDI}	V _{DDI} /2.5	V _{OL} /40	(V _{DDI} - V _{OH})/60	

1. V_{ICM} is the input common mode voltage.

2. V_{ID} is the input differential voltage (Q - Q).

3. V_{OH} is the single-ended high-output voltage.

4. I_{OL}/I_{OH} Units for impedance standards in Amps (not mA).

5. V_{OH_MAX} based on external pull-up termination (pseudo-open drain).

2.5.3.4 HSIO On-Die Termination

Table 15 • On-Die Termination Calibration Accuracy Specifications for HSIO Bank

Parameter	Description	Min (%)	Typ	Max (%)	Unit	Condition
Single-ended thevenin termination ^{1, 2}	Internal parallel thevenin termination	-40	50	20	Ω	V _{DDI} = 1.8 V/ 1.5 V/ 1.35 V/1.2 V
		-40	75	20	Ω	V _{DDI} = 1.8 V
		-40	150	20	Ω	V _{DDI} = 1.8 V
		-20	20	20	Ω	V _{DDI} = 1.5 V/1.35 V
		-20	30	20	Ω	V _{DDI} = 1.5 V/1.35 V
		-20	40	20	Ω	V _{DDI} = 1.5 V/1.35 V
		-20	60	20	Ω	V _{DDI} = 1.5 V/1.35 V
		-20	120	20	Ω	V _{DDI} = 1.5 V/1.35 V
		-20	60	20	Ω	V _{DDI} = 1.2 V
Single-ended termination to V _{DDI} ³	Internal parallel termination to V _{DDI}	-20	120	20	Ω	V _{DDI} = 1.8 V/1.5 V
		-20	240	20	Ω	V _{DDI} = 1.8 V/1.5 V
		-20	34	20	Ω	V _{DDI} = 1.2 V
		-20	40	20	Ω	V _{DDI} = 1.2 V
		-20	48	20	Ω	V _{DDI} = 1.2 V
		-20	60	20	Ω	V _{DDI} = 1.2 V
		-20	80	20	Ω	V _{DDI} = 1.2 V
		-20	120	20	Ω	V _{DDI} = 1.2 V
		-20	240	20	Ω	V _{DDI} = 1.2 V
Single-ended termination to V _{SS} ⁴	Internal parallel termination to V _{SS}	-20	120	20	Ω	V _{DDI} = 1.8 V/1.5 V
		-20	240	20	Ω	V _{DDI} = 1.8 V/1.5 V
		-20	120	20	Ω	V _{DDI} = 1.2 V
		-20	240	20	Ω	V _{DDI} = 1.2 V
		-20	40	20	Ω	V _{DDI} = 1.1 V
		-20	48	20	Ω	V _{DDI} = 1.1 V
		-20	60	20	Ω	V _{DDI} = 1.1 V
		-20	80	20	Ω	V _{DDI} = 1.1 V
		-20	120	20	Ω	V _{DDI} = 1.1 V
		-20	240	20	Ω	V _{DDI} = 1.1 V

1. Thevenin impedance is calculated based on independent P and N as measured at 50% of V_{DDI}.

2. For 50 Ω/75 Ω/150 Ω cases, nearest supported values of 40 Ω/60 Ω/120 Ω are used.

3. Measured at 50% of V_{DDI}.

4. Measured at 50% of V_{DDI}.

2.5.3.5 GPIO On-Die Termination

Table 16 • On-Die Termination Calibration Accuracy Specifications for GPIO Bank

Parameter	Description	Min (%)	Typ	Max (%)	Unit	Condition
Differential termination ¹	Internal differential termination	-20	100	25	Ω	$V_{CM} < 0.7\text{ V}$
		-20		25		$0.7\text{ V} < V_{CM} < 0.9\text{ V}$
		-20		25		$0.9\text{ V} < V_{CM}$
Single-ended thevenin termination ^{2, 3}	Internal parallel thevenin termination	-40	50	20	Ω	$V_{DDI} = 1.8\text{ V}/1.5\text{ V}$
		-40	75	20	Ω	$V_{DDI} = 1.8\text{ V}$
		-40	150	20	Ω	$V_{DDI} = 1.8\text{ V}$
		-20	20	20	Ω	$V_{DDI} = 1.5\text{ V}$
		-20	30	20	Ω	$V_{DDI} = 1.5\text{ V}$
		-20	40	20	Ω	$V_{DDI} = 1.5\text{ V}$
		-20	60	20	Ω	$V_{DDI} = 1.5\text{ V}$
		-20	120	20	Ω	$V_{DDI} = 1.5\text{ V}$
		-20	60	20	Ω	$V_{DDI} = 1.2\text{ V}$
		-20	120	20	Ω	$V_{DDI} = 1.2\text{ V}$
Single-ended termination to V_{DDI} ⁴	Internal parallel termination to V_{DDI}	-20	120	20	Ω	$V_{DDI} = 1.8\text{ V}/1.5\text{ V}$
		-20	240	20	Ω	$V_{DDI} = 1.8\text{ V}/1.5\text{ V}$
		-20	120	20	Ω	$V_{DDI} = 1.2\text{ V}$
		-20	240	20	Ω	$V_{DDI} = 1.2\text{ V}$
Single-ended termination to V_{SS} ⁵	Internal parallel termination to V_{SS}	-20	240	20	Ω	$V_{DDI} = 3.3\text{ V}$
		-20	120	20	Ω	$V_{DDI} = 2.5\text{ V}/1.8\text{ V}/1.5\text{ V}/1.2\text{ V}$
		-20	240	20	Ω	$V_{DDI} = 2.5\text{ V}/1.8\text{ V}/1.5\text{ V}/1.2\text{ V}$

1. Measured across P to N with 400 mV bias.

2. Thevenin impedance is calculated based on independent P and N as measured at 50% of V_{DDI} .

3. For 50 Ω /75 Ω /150 Ω cases, nearest supported values of 40 Ω /60 Ω /120 Ω are used.

4. Measured at 50% of V_{DDI} .

5. Measured at 50% of V_{DDI} .

2.5.3.6 LVDS

LVDS operation is supported in GPIO banks. The following tables provide DC specifications with various I/O bank voltage supplies of 3.3 V, 2.5 V, and 1.8 V.

2.5.3.6.1 3.3 V LVDS

Table 17 • GPIO 3.3 V LVDS DC Specifications

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Supply voltage ¹	V _{DDI}	3.135	3.300	3.465	V	
Output high-voltage for P and N	V _{OH}			1.675	V	R _T = 100 Ω across P and N signals
Output low-voltage for P and N	V _{OL}	0.700			V	R _T = 100 Ω across P and N signals
Differential output voltage	V _{ODIFF}	247	350	600	mV	R _T = 100 Ω across P and N signals
Output common mode	V _{OCM}	1.000	1.250	1.425	V	R _T = 100 Ω across P and N signals
Differential input voltage	V _{IDIFF}	100	350	600	mV	
Input common mode	V _{ICM}	0.050	1.200	2.350	V	

1. Differential inputs can be placed in I/O banks with a different V_{DDI} from the required level for outputs. For more information, see [UG0686: PolarFire FPGA User I/O User Guide](#).

2.5.3.6.2 2.5 V LVDS

Table 18 • GPIO 2.5 V LVDS DC Specifications

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Supply voltage ¹	V _{DDI}	2.375	2.500	2.625	V	
Output high-voltage for P and N	V _{OH}			1.675	V	R _T = 100 Ω across P and N signals
Output low-voltage for P and N	V _{OL}	0.700			V	R _T = 100 Ω across P and N signals
Differential output voltage	V _{ODIFF}	247	350	600	mV	R _T = 100 Ω across P and N signals
Output common mode	V _{OCM}	1.000	1.250	1.425	V	R _T = 100 Ω across P and N signals
Differential input voltage	V _{IDIFF}	100	350	600	mV	
Input common mode ²	V _{ICM}	0.050	1.200	2.350	V	

1. Differential inputs can be placed in I/O banks with a different V_{DDI} from the required level for outputs. For more information, see [UG0686: PolarFire FPGA I/O User Guide](#).
2. V_{ICM} max must be less than V_{DDI} – .3 V.

2.5.3.6.3 1.8 V LVDS

Table 19 • GPIO 1.8 V LVDS Receiver DC Specifications

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage ¹	V _{DDI}	1.710	1.800	1.890	V
Differential input voltage	V _{IDIFF}	0.100	0.350	0.600	V
Input common mode ²	V _{ICM}	0.050	0.800	1.650	V

1. Differential inputs can be placed in I/O banks with a different V_{DDI} from the required level for outputs. For more information, see [UG0686: PolarFire FPGA I/O User Guide](#).
2. For LVDS18, AC transient purposes, V_{ICM} cannot exceed 0.95 V.

2.6 AC Switching Characteristics

2.6.1 I/O Standards Specifications

This section describes I/O delay measurement methodology, buffer speed, switching characteristics, digital latency, gearing training calibration, and maximum physical interface (PHY) rate for memory interface IP.

2.6.1.1 Input Delay Measurement Methodology

Table 20 • Input Delay Measurement Methodology

Standard	Description	V_L^1	V_H^1	V_{ID}^2	V_{ICM}^2	$V_{MEAS}^{3,4}$	$V_{REF}^{1,5}$	Unit
PCI33	PCIE 3.3 V	0.1	3.2			1.32		V
LVTTL33	LVTTL 3.3 V	0.1	3.2			1.75		V
LVC MOS33	LVC MOS 3.3 V	0.1	3.2			1.75		V
LVC MOS25	LVC MOS 2.5 V	0.1	2.4			1.25		V
LVC MOS18	LVC MOS 1.8 V	0.1	1.7			0.90		V
LVC MOS15	LVC MOS 1.5 V	0.1	1.4			0.75		V
LVC MOS12	LVC MOS 1.2 V	0.1	1.1			0.60		V
SSTL25_I	SSTL 2.5 V Class I	$V_{REF} - 1.15$	$V_{REF} + 1.15$			V_{REF}	1.25	V
SSTL25_II	SSTL 2.5 V Class II	$V_{REF} - 1.15$	$V_{REF} + 1.15$			V_{REF}	1.25	V
SSTL18_I	SSTL 1.8 V Class I	$V_{REF} - 0.8$	$V_{REF} + 0.8$			V_{REF}	0.90	V
SSTL18_II	SSTL 1.8 V Class II	$V_{REF} - 0.8$	$V_{REF} + 0.8$			V_{REF}	0.90	V
SSTL15_I	SSTL 1.5 V Class I	$V_{REF} - .65$	$V_{REF} + .65$			V_{REF}	0.75	V
SSTL15_II	SSTL 1.5 V Class II	$V_{REF} - .65$	$V_{REF} + .65$			V_{REF}	0.75	V
SSTL135_I	SSTL 1.35 V Class I	$V_{REF} - .575$	$V_{REF} + .575$			V_{REF}	0.675	V
SSTL135_II	SSTL 1.35 V Class II	$V_{REF} - .575$	$V_{REF} + .575$			V_{REF}	0.675	V
HSTL15_I	HSTL 1.5 V Class I	$V_{REF} - .65$	$V_{REF} + .65$			V_{REF}	0.75	V
HSTL15_II	HSTL 1.5 V Class II	$V_{REF} - .65$	$V_{REF} + .65$			V_{REF}	0.75	V
HSTL135_I	HSTL 1.35 V Class I	$V_{REF} - .575$	$V_{REF} + .575$			V_{REF}	0.675	V
HSTL135_II	HSTL 1.35 V Class II	$V_{REF} - .575$	$V_{REF} + .575$			V_{REF}	0.675	V
HSTL12	HSTL 1.2 V	$V_{REF} - .5$	$V_{REF} + .5$			V_{REF}	0.60	V
HSUL18_I	HSUL 1.8 V Class I	$V_{REF} - 0.8$	$V_{REF} + 0.8$			V_{REF}	0.90	V
HSUL18_II	HSUL 1.8 V Class II	$V_{REF} - 0.8$	$V_{REF} + 0.8$			V_{REF}	0.90	V
HSUL12	HSUL 1.2 V	$V_{REF} - .5$	$V_{REF} + .5$			V_{REF}	0.60	V
POD12_I	Pseudo open drain (POD) logic 1.2 V Class I	$V_{REF} - .16$	$V_{REF} + .65$			V_{REF}	0.84	V
POD12_II	POD 1.2 V Class II	$V_{REF} - .16$	$V_{REF} + .65$			V_{REF}	0.84	V
LVSTL11_I	Low-voltage swing terminated (LVSTL) logic 1.1 V Class I	$V_{REF} - .083$	$V_{REF} + .083$			V_{REF}	0.183	V
LVSTL11_II	LVSTL 1.1 V Class II	$V_{REF} - .12$	$V_{REF} + .12$			V_{REF}	0.22	V
LVDS33	Low-voltage differential signaling (LVDS) 3.3 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V

Table 20 • Input Delay Measurement Methodology (continued)

Standard	Description	V_L^1	V_H^1	V_{ID}^2	V_{ICM}^2	$V_{MEAS}^{3,4}$	$V_{REF}^{1,5}$	Unit
LVDS25	LVDS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
LVDS18 ⁶	LVDS 1.8 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.900	0		V
RSDS33	RSDS 3.3 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
RSDS25	RSDS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
RSDS18	RSDS 1.8 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
MiniLVDS33	Mini-LVDS 3.3 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
MiniLVDS25	Mini-LVDS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
MiniLVDS18	Mini-LVDS 1.8 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
SubLVDS33	Sub-LVDS 3.3 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.900	0		V
SubLVDS25	Sub-LVDS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.900	0		V
SubLVDS18	Sub-LVDS 1.8 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.900	0		V
PPDS33	Point-to-point differential signaling 3.3 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.800	0		V
PPDS25	PPDS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.800	0		V
PPDS18	PPDS 1.8 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.800	0		V
SLVS33	Scalable low-voltage signaling 3.3 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.200	0		V
SLVS25	SLVS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.200	0		V
SLVS18	SLVS 1.8 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.200	0		V
HCSL33	High-speed current steering logic (HCSL) 3.3 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.350	0		V
HCSL25	HCSL 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.350	0		V
HCSL18	HCSL 1.8 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.350	0		V
BLVDSE25 ⁷	Bus LVDS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
MLVDSE25 ⁷	Multipoint LVDS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
LVPECL33	Low-voltage positive emitter coupled logic	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.650	0		V
LVPECLE33 ⁷	Low-voltage positive emitter coupled logic	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.650	0		V
MIPI12 (high-speed)	Mobile industry processor interface	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.200	0		V
SSTL25D_I	Differential SSTL 2.5 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
SSTL25D_II	Differential SSTL 2.5 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
SSTL18D_I	Differential SSTL 1.8 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.900	0		V
SSTL18D_II	Differential SSTL 1.8 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.900	0		V
SSTL15	Differential SSTL 1.5 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.750	0		V

Table 20 • Input Delay Measurement Methodology (continued)

Standard	Description	V_L^1	V_H^1	V_{ID}^2	V_{ICM}^2	$V_{MEAS}^{3,4}$	$V_{REF}^{1,5}$	Unit
SSTL135	Differential SSTL 1.5 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.750	0		V
HSTL15D_I	Differential HSTL 1.5 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.750	0		V
HSTL15D_II	Differential HSTL 1.5 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.750	0		V
HSTL135D_I	Differential HSTL 1.35 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.675	0		V
HSTL135D_II	Differential HSTL 1.35 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.675	0		V
HSTL12	Differential HSTL 1.2 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.600	0		V
HSUL18D_I	Differential HSUL 1.8 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.900	0		V
HSUL18D_II	Differential HSUL 1.8 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.900	0		V
HSUL12	Differential HSUL 1.2 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.600	0		V
POD12D_I	Differential POD 1.2 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.600	0		V
POD12D_II	Differential POD 1.2 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.600	0		V
LVSTLD_I	Differential LVSTL 1.1 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.550	0		V
LVSTLD_II	Differential LVSTL 1.1 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.550	0		V

1. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst-case of these measurements. V_{REF} values listed are typical. Input waveform switches between V_L and V_H . All rise and fall times must be 1 V/ns.
2. Differential receiver standards all use 250 mV V_{ID} for timing. V_{ICM} is different between different standards.
3. Input voltage level from which measurement starts.
4. The value given is the differential input voltage.
5. This is an input voltage reference that bears no relation to the V_{REF}/V_{MEAS} parameters found in IBIS models and/or noted in [Figure 1](#), page 21.
6. V_{ICM} cannot exceed 0.95 V.
7. Emulated bi-directional interface.

2.6.1.2 Output Delay Measurement Methodology

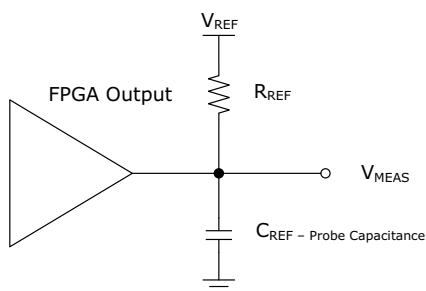
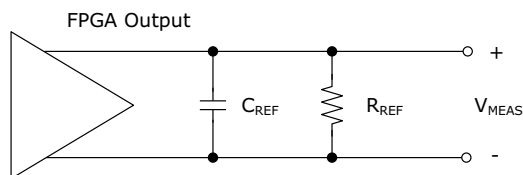
Table 21 • Output Delay Measurement Methodology

Standard	Description	R _{REF} (Ω)	C _{REF} (pF)	V _{MEAS} (V)	V _{REF} (V)
PCI33	PCIE 3.3 V	25	10	1.65	
LVTTL33	LVTTL 3.3 V	1M	0	1.65	
LVC MOS33	LVC MOS 3.3 V	1M	0	1.65	
LVC MOS25	LVC MOS 2.5 V	1M	0	1.25	
LVC MOS18	LVC MOS 1.8 V	1M	0	0.90	
LVC MOS15	LVC MOS 1.5 V	1M	0	0.75	
LVC MOS12	LVC MOS 1.2 V	1M	0	0.60	
SSTL25_I	Stub-series terminated logic (SSTL) 2.5 V Class I	50	0	V _{REF}	1.25
SSTL25_II	SSTL 2.5 V Class II	50	0	V _{REF}	1.25
SSTL18_I	SSTL 1.8 V Class I	50	0	V _{REF}	0.9
SSTL18_II	SSTL 1.8 V Class II	50	0	V _{REF}	0.9
SSTL15_I	SSTL 1.5 V Class I	50	0	V _{REF}	0.75
SSTL15_II	SSTL 1.5 V Class II	50	0	V _{REF}	0.75
SSTL135_I	SSTL 1.35 V Class I	50	0	V _{REF}	0.675
SSTL135_II	SSTL 1.35 V Class II	50	0	V _{REF}	0.675
HSTL15_I	High-speed transceiver logic (HSTL) 1.5 V Class I	50	0	V _{REF}	0.75
HSTL15_II	HSTL 1.5 V Class II	50	0	V _{REF}	0.75
HSTL135_I	HSTL 1.35 V Class I	50	0	V _{REF}	0.675
HSTL135_II	HSTL 1.35 V Class II	50	0	V _{REF}	0.675
HSTL12	HSTL 1.2 V	50	0	V _{REF}	0.6
HSUL18_I	High-speed unterminated logic (HSUL) 1.8 V Class I	50	0	V _{REF}	0.9
HSUL18_II	HSUL 1.8 V Class II	50	0	V _{REF}	0.9
HSUL12	HSUL 1.2 V	50	0	V _{REF}	0.6
POD12_I	Pseudo open drain (POD) logic 1.2 V Class I	50	0	V _{REF}	0.84
POD12_II	POD 1.2 V Class II	50	0	V _{REF}	0.84
LVSTL11_I	LVSTL 1.1 V Class I	50	0	V _{REF}	0.183
LVSTL11_II	LVSTL 1.1 V Class II	50	0	V _{REF}	0.22
LVDS33	LVDS 3.3 V	100	0	0 ¹	0
LVDS25	LVDS 2.5 V	100	0	0 ¹	0
LVDS18	LVDS 1.8 V	100	0	0 ¹	0
RS DS33	Reduced swing differential signaling (RS DS) 3.3 V	100	0	0 ¹	0
RS DS25	RS DS 2.5 V	100	0	0 ¹	0
RS DS18	RS DS 1.8 V	100	0	0 ¹	0
MiniLVDS33	Mini-LVDS 3.3 V	100	0	0 ¹	0

Table 21 • Output Delay Measurement Methodology (continued)

Standard	Description	R_{REF} (Ω)	C_{REF} (pF)	V_{MEAS} (V)	V_{REF} (V)
MiniLVDS25	Mini-LVDS 2.5 V	100	0	0 ¹	0
MiniLVDS18	Mini-LVDS 1.8 V	100	0	0 ¹	0
SubLVDS33	Sub-LVDS 3.3 V	100	0	0 ¹	0
SubLVDS25	Sub-LVDS 2.5 V	100	0	0 ¹	0
SubLVDS18	Sub-LVDS 1.8 V	100	0	0 ¹	0
PPDS33	Point-to-point differential signaling 3.3 V	100	0	0 ¹	0
PPDS25	PPDS 2.5 V	100	0	0 ¹	0
PPDS18	PPDS 1.8 V	100	0	0 ¹	0
SLVS33	Scalable low-voltage signaling 3.3 V	100	0	0 ¹	0
SLVS25	SLVS 2.5 V	100	0	0 ¹	0
SLVS18	SLVS 1.8 V	100	0	0 ¹	0
HCSL33	High-speed current steering logic 3.3 V	100	0	0 ¹	0
HCSL25	HCSL 2.5 V	100	0	0 ¹	0
HCSL18	HCSL 1.8 V	100	0	0 ¹	0
BUSLVDSE25	Bus LVDS	100	0	0 ¹	0
MLVDSE25	Multipoint LVDS 2.5 V	100	0	0 ¹	0
LVPECLE33	Low-voltage positive emitter-coupled logic	100	0	0 ¹	0
MIPIE25	Mobile industry processor interface 2.5 V	100	0	0 ¹	0

1. The value given is the differential output voltage.

Figure 1 • Output Delay Measurement—Single-Ended Test Setup**Figure 2 • Output Delay Measurement—Differential Test Setup**

2.6.1.3 Input Buffer Speed

Table 22 • HSIO Maximum Input Buffer Speed

Standard	STD	–1	Unit
LVDS18	1250	1250	Mb/s
RSDS18	800	800	Mb/s
MiniLVDS18	800	800	Mb/s
SUBLVDS18	800	800	Mb/s
PPDS18	800	800	Mb/s
SLVS18	800	800	Mb/s
SSTL18_I	800	1066	Mb/s
SSTL18_II	800	1066	Mb/s
SSTL15_I	1066	1333	Mb/s
SSTL15_II	1066	1333	Mb/s
SSTL135_I	1066	1333	Mb/s
SSTL135_II	1066	1333	Mb/s
HSTL15_I	900	1100	Mb/s
HSTL15_II	900	1100	Mb/s
HSTL135_I	1066	1066	Mb/s
HSTL135_II	1066	1066	Mb/s
HSUL18_I	400	400	Mb/s
HSUL18_II	400	400	Mb/s
HSUL12	1066	1333	Mb/s
HSTL12	1066	1266	Mb/s
POD12_I	1333	1600	Mb/s
POD12_II	1333	1600	Mb/s
LVSTL11_I	1333	1600	Mb/s
LVSTL11_II	1333	1600	Mb/s
LVC MOS18 (12 mA)	500	500	Mb/s
LVC MOS15 (10 mA)	500	500	Mb/s
LVC MOS12 (8 mA)	300	300	Mb/s

Table 23 • GPIO Maximum Input Buffer Speed

Standard	STD	-1	Unit
LVDS25/LVDS33	1250	1250	Mb/s
RSDS25/RSDS33	800	800	Mb/s
MINILVDS25/MINILVDS33	800	800	Mb/s
SUBLVDS25/SUBLVDS33	800	800	Mb/s
PPDS25/PPDS33	800	800	Mb/s
SLVS25/SLVS33	800	800	Mb/s
SLVSE15	800	800	Mb/s
HCSL25/HCSL33	800	800	Mb/s
BUSLVDSE25	800	800	Mb/s
MLVDSE25	800	800	Mb/s
LVPECL33	800	800	Mb/s
MIPI25/MIPI33	800	800	Mb/s
SSTL25_I	800	800	Mb/s
SSTL25_II	800	800	Mb/s
SSTL18_I	800	800	Mb/s
SSTL18_II	800	800	Mb/s
SSTL15_I	800	1066	Mb/s
SSTL15_II	800	1066	Mb/s
HSTL15_I	900	900	Mb/s
HSTL15_II	900	900	Mb/s
HSUL18_I	400	400	Mb/s
HSUL18_II	400	400	Mb/s
PCI33	500	500	Mb/s
LVTTTL33 (20 mA)	500	500	Mb/s
LVC MOS33 (20 mA)	500	500	Mb/s
LVC MOS25 (16 mA)	500	500	Mb/s
LVC MOS18 (12 mA)	500	500	Mb/s
LVC MOS15 (10 mA)	500	500	Mb/s
LVC MOS12 (8 mA)	300	300	Mb/s

Note: All SSTLD/HSTLD/HSULD/LVSTLD/PODD type receivers use the LVDS differential receiver.

2.6.1.4 Output Buffer Speed

Table 24 • HSIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
SSTL18_I	800	1066	Mb/s
SSTL18_II	800	1066	Mb/s
SSTL18D_I	800	1066	Mb/s
SSTL18D_II	800	1066	Mb/s
SSTL15_I	1066	1333	Mb/s
SSTL15_II	1066	1333	Mb/s
SSTL15D_I	1066	1333	Mb/s
SSTL15D_II	1066	1333	Mb/s
SSTL135_I	1066	1333	Mb/s
SSTL135_II	1066	1333	Mb/s
SSTL135D_I	1066	1333	Mb/s
SSTL135D_II	1066	1333	Mb/s
HSTL15_I	900	1100	Mb/s
HSTL15_II	900	1100	Mb/s
HSTL15D_I	900	1100	Mb/s
HSTL15D_II	900	1100	Mb/s
HSTL135_I	1066	1066	Mb/s
HSTL135_II	1066	1066	Mb/s
HSTL135D_I	1066	1066	Mb/s
HSTL135D_II	1066	1066	Mb/s
HSUL18_I	400	400	Mb/s
HSUL18_II	400	400	Mb/s
HSUL18D_II	400	400	Mb/s
HSUL12	1066	1333	Mb/s
HSUL12D_I	1066	1333	Mb/s
HSTL12	1066	1266	Mb/s
HSTL12D_I	1066	1266	Mb/s
POD12_I	1333	1600	Mb/s
POD12_II	1333	1600	Mb/s
LVSTL11_I	1333	1600	Mb/s
LVSTL11_II	1333	1600	Mb/s
LVC MOS18 (12 mA)	500	500	Mb/s
LVC MOS15 (10 mA)	500	500	Mb/s
LVC MOS12 (8 mA)	250	300	Mb/s

Table 25 • GPIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
LVDS25	1250	1600	Mb/s
RSDS25	800	800	Mb/s
MINILVDS25	800	800	Mb/s
SUBLVDS25	800	800	Mb/s
PPDS25	800	800	Mb/s
SLVSE15	500	500	Mb/s
BUSLVDSE25	500	500	Mb/s
MLVDSE25	500	500	Mb/s
LVPECLE33	500	500	Mb/s
MIPIE25	500	500	Mb/s
SSTL25_I	800	800	Mb/s
SSTL25_II	800	800	Mb/s
SSTL25D_I	800	800	Mb/s
SSTL25D_II	800	800	Mb/s
SSTL18_I	800	800	Mb/s
SSTL18_II	800	800	Mb/s
SSTL18D_I	800	800	Mb/s
SSTL18D_II	800	800	Mb/s
SSTL15_I	800	1066	Mb/s
SSTL15_II	800	1066	Mb/s
SSTL15D_I	800	1066	Mb/s
SSTL15D_II	800	1066	Mb/s
HSTL15_I	900	900	Mb/s
HSTL15_II	900	900	Mb/s
HSTL15D_I	900	900	Mb/s
HSTL15D_II	900	900	Mb/s
HSUL18_I	400	400	Mb/s
HSUL18_II	400	400	Mb/s
HSUL18D_I	400	400	Mb/s
HSUL18D_II	400	400	Mb/s
PCI33	500	500	Mb/s
LVTTTL33 (20 mA)	500	500	Mb/s
LVC MOS33 (20 mA)	500	500	Mb/s
LVC MOS25 (16 mA)	500	500	Mb/s
LVC MOS18 (12 mA)	500	500	Mb/s
LVC MOS15 (10 mA)	500	500	Mb/s
LVC MOS12 (8 mA)	250	300	Mb/s

2.6.1.5 Maximum PHY Rate for Memory Interface IP

Table 26 • Maximum PHY Rate for Memory Interfaces IP for HSIO Banks

Memory Standard	Gearing Ratio	V _{DDAUX}	V _{DDI}	Mbps		Fabric MHz	
				STD	–1	STD	–1
DDR4 ¹	8:1	1.8 V	1.2 V	1333	1600	167	200
DDR3	8:1	1.8 V	1.5 V	1067	1333	133	167
DDR3L	8:1	1.8 V	1.35 V	1067	1333	133	167
LPDDR3	8:1	1.8 V	1.2 V	1067	1333	133	167
LPDDR2	8:1	1.8 V	1.2 V	1067	1067	133	133
	4:1	1.8 V	1.2 V	600	600	150	150
QDRII+	8:1	1.8 V	1.5 V	900	1100	113	138
RLDRAM3 ²	8:1	1.8 V	1.35 V	1067	1067	133	133
	4:1	1.8 V	1.35 V	667	800	167	200
	2:1	1.8 V	1.35 V	333	400	167	200
RLDRAM2 ²	8:1	1.8 V	1.8 V	800	1067	100	133
	4:1	1.8 V	1.8 V	667	800	167	200
	2:1	1.8 V	1.8 V	333	400	167	200

1. Table represents DDR4 in the FC1152 package for all data widths without ECC and CRC enabled. DDR4 in the FCG484 and FCG484 packages are limited to 16-bit interfaces for 1600 Mbps support.
2. RLDRAM2 and RLDRAM3 are not supported with a soft IP controller currently.

Table 27 • Maximum PHY Rate for Memory Interfaces IP for GPIO Banks

Memory Standard	Gearing Ratio	V _{DDAUX}	V _{DDI}	Mbps		Fabric MHz	
				STD	–1	STD	–1
DDR3	8:1	2.5 V	1.5 V	800	1067	100	133
QDRII+	8:1	2.5 V	1.5 V	900	900	113	113
RLDRAM2 ¹	4:1	2.5 V	1.8 V	800	800	200	200
	2:1	2.5 V	1.8 V	400	400	200	200

1. RLDRAM2 is not supported with a soft IP controller currently.

2.6.1.6 User I/O Switching Characteristics

For more information about user I/O timing, see the *PolarFire I/O Timing Spreadsheet* (to be released).

2.6.1.6.1 I/O Digital

Table 28 • I/O Digital Receive Single-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD			–1			Unit	Clock-to-Data Condition
			Min	Typ	Max	Min	Typ	Max		
F _{MAX}	RX_SDR_G	Rx SDR							MHz	From a global clock source, aligned
F _{MAX}	RX_SDR_R								MHz	From a regional clock source, aligned
F _{MAX}	RX_SDR_G_DLL								MHz	From a global clock source aligned with DLL CID ¹
F _{MAX}	RX_SDR_R_DLL								MHz	From a regional clock source aligned with DLL CID ¹

1. Allows the use of customer defined input delay static values to achieve timing constraints. The value of an input delay that uses the same delay step size as the DLL is specified in [Table 38](#), page 35.

Table 29 • I/O Digital Receive Double-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD			–1			Unit	Clock-to-Data Condition
			Min	Typ	Max	Min	Typ	Max		
F _{MAX}	RX_DDR_G_A	Rx DDR							MHz	From a global clock source, aligned with DLL delay
F _{MAX}	RX_DDR_R_A								MHz	From a regional clock source, aligned with DLL delay
F _{MAX}	RX_DDR_L_A								MHz	From a Lane clock source, aligned with DLL delay
F _{MAX}	RX_DDR_G_C								MHz	From a global clock source, centered
F _{MAX}	RX_DDR_R_C								MHz	From a regional clock source, centered
F _{MAX}	RX_DDR_L_C								MHz	From a Lane clock source, centered
F _{MAX} 2:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned with DLL delay
F _{MAX} 4:1									MHz	
F _{MAX} 8:1									MHz	

Table 29 • I/O Digital Receive Double-Data Rate Switching Characteristics (continued)

Parameter	Interface Name	Topology	STD			–1			Unit	Clock-to-Data Condition
			Min	Typ	Max	Min	Typ	Max		
Data valid window	RX_DDRX_B_DYN	Rx DDR digital mode							ns	From a HS_IO_CLK clock source, dynamic delay
F_{MAX} 2:1									MHz	
F_{MAX} 4:1									MHz	
F_{MAX} 8:1									MHz	

Table 30 • I/O Digital Transmit Single-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD			–1			Unit	Forwarded Clock to Data Skew
			Min	Typ	Max	Min	Typ	Max		
Output data skew	TX_SDR_G	Tx SDR							ns	From a global clock source, aligned ¹
Output F_{MAX}									MHz	
Output data skew	TX_SDR_R								ns	From a regional clock source, aligned ¹
Output maximum frequency									MHz	

1. A centered clock-to-data interface can be created with a negedge launch of the data.

Table 31 • I/O Digital Transmit Double-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD			–1			Unit	Forwarded Clock to Data Skew
			Min	Typ	Max	Min	Typ	Max		
Output data skew	TX_DDR_G_A	Tx DDR							ns	From a global clock source, aligned
Output F _{MAX}									MHz	
Output data skew	TX_DDR_R_A								ns	From a regional clock source, aligned
Output F _{MAX}									MHz	
Output data skew	TX_DDRX_B_A	Tx DDR digital mode							ns	From a HS_IO_CLK clock source, aligned with PLL
Output F _{MAX} 2:1									MHz	
Output F _{MAX} 4:1									MHz	
Output F _{MAX} 8:1									MHz	
Output data skew	TX_DDRX_B_DYN								ns	From a HS_IO_CLK clock source, dynamic with PLL
Output F _{MAX} 2:1									MHz	
Output F _{MAX} 4:1									MHz	
Output F _{MAX} 8:1									MHz	
In delay, out delay, DLL delay step sizes									ns	

2.6.1.7 I/O Digital Latency

Table 32 • I/O Digital Receive Double-Data Rate Latency Characteristics

Parameter	Interface Name	Gear Ratio	Topology	STD			–1			Unit	Clock-to-Data Condition
				Min	Typ	Max	Min	Typ	Max		
From pad to fabric ^{1, 2}	RX_SDR_G	1	Rx SDR mode	1			1			UI	From SCLK, static delay
	RX_SDR_R	1	Rx SDR mode	1			1			UI	
	RX_DDR_G_A	1	Rx DDR digital mode	1			1			UI	
	RX_DDR_R_A	1	Rx DDR digital mode	1			1			UI	
	RX_DDR_L_A	1	RGMII	1			1			UI	From lane clock (DQS), static delay
	RX_DDR_B_A	1	Rx DDR digital Mode	1			1			UI	From a HS_IO_CLK clock source, static delay
	RX_DDR_G_C	1	Rx DDR digital mode	1			1			UI	From SCLK, static delay
	RX_DDR_R_C	1	Rx DDR digital mode	1			1			UI	
	RX_DDR_L_C	1	Rx DDR digital mode	1			1			UI	From lane clock (DQS), static delay
	RX_DDR_B_C	1	Rx DDR digital mode	1			1			UI	From a HS_IO_CLK clock source, static delay
	RX_DDRX_B_A	2	Rx DDR digital mode	4			4			UI	
	RX_DDRX_B_A	3.5	Rx Video7	6			6			UI	
	RX_DDRX_B_A	4	Rx DDR digital mode	7			7			UI	
	RX_DDRX_B_A_DYN	2	Rx DDR digital mode (trained)	9			9			UI	From a HS_IO_CLK clock source, dynamic delay
	RX_DDRX_B_A_DYN	3.5	Rx Video7	6			6			UI	
	RX_DDRX_B_A_DYN	4	Rx DDR digital mode (trained)	7			7			UI	
	IOD_CDR_TX	5	Rx SGMII	9			9			UI	Clock recovered from data, lane clock, dynamic delay

1. UI is referenced to the high-speed pin side clock period.

2. RX latency measured from pad-to-fabric interface.

Table 33 • I/O Digital Transmit Double-Data Rate Latency Characteristics

Parameter	Interface Name	Gear Ratio	Topology	STD			–1			Unit	Clock to Data Condition
				Min	Typ	Max	Min	Typ	Max		
From fabric to pad ¹	TX_SDR_G	1	Tx SDR digital mode		1.0			1.0		UI	From a SCLK, static delay
	TX_SDR_R	1	Tx SDR digital mode		1.0			1.0		UI	From a SCLK, static delay
	TX_DDR_G_A	1	Tx SDR digital mode		2.5			2.5		UI	From a SCLK, static delay
	TX_DDR_R_A	1	Tx DDR digital mode		2.5			2.5		UI	From a SCLK, static delay
	TX_DDR_G_C	1	Tx DDR digital mode		2.5			2.5		UI	From a SCLK, static delay
	TX_DDR_R_C	1	Tx DDR digital mode		2.5			2.5		UI	From a SCLK, static delay
	TX_DDRX_B_A	2	Tx DDR digital mode		5.5			5.5		UI	From a HS_IO_CLK clock source, static delay, with PLL
	TX_DDRX_B_A	3.5	Tx Video7		6.0			6.0		UI	From a HS_IO_CLK clock source, static delay, with PLL
	TX_DDRX_B_A	4	Tx DDR digital mode		10.5			10.5		UI	From a HS_IO_CLK clock source, static delay, with PLL
	TX_DDRX_B_A	5	Tx SGMII		13.5			13.5		UI	From a HS_IO_CLK clock source, static delay, with PLL
	TX_DDRX_B_DYN	2	Tx DDR digital mode (trained)		5.5			5.5		UI	From a HS_IO_CLK clock source, dynamic delay, with PLL
	TX_DDRX_B_DYN	4	Tx DDR digital mode (trained)		10.5			10.5		UI	From a HS_IO_CLK clock source, dynamic delay, with PLL

1. UI is referenced to the high-speed pin side clock period.

2.6.1.8 I/O Digital Training Calibration

Table 34 • I/O Digital Double-Data Rate Calibration Timing

Parameter	I/O Type	STD		–1		Unit
		Min	Max	Min	Max	
User initiated I/O calibration	GPIO		2.2		2.2	ns
	HSIO		2.2		2.2	ns

Table 35 • I/O Digital Training Timing

Parameter	I/O Type	STD		-1		Unit
		Min	Max	Min	Max	
User initiated I/O training	RX_SDR_G					ns
	RX_SDR_R					ns
	RX_DDR_G_A					ns
	RX_DDR_R_A					ns
	RX_DDR_L_A					ns
	RX_DDR_B_A					ns
	RX_DDR_G_C					ns
	RX_DDR_R_C					ns
	RX_DDR_L_C					ns
	RX_DDR_B_C					ns
	RX_DDRX_B_A					ns
	RX_DDRX_B_A					ns
	RX_DDRX_B_A					ns
	RX_DDRX_B_A_DYN					ns
	RX_DDRX_B_A_DYN					ns
	RX_DDRX_B_A_DYN					ns
	IOD_CDR_TX					ns
	TX_SDR_G					ns
	TX_SDR_R					ns
	TX_DDR_G_A					ns
	TX_DDR_R_A					ns
	TX_DDR_G_C					ns
	TX_DDR_R_C					ns
	TX_DDRX_B_A					ns
	TX_DDRX_B_A					ns
	TX_DDRX_B_A					ns
	TX_DDRX_B_A					ns
	TX_DDRX_B_DYN					ns
	TX_DDRX_B_DYN					ns

2.6.2 Clocking Specifications

This section describes the PLL and DLL clocking and oscillator specifications.

2.6.2.1 Clocking

Table 36 • Global and Regional Clock Characteristics

		Temperature Range: 0 °C to 100 °C				Unit	Condition
		V _{DD} = 1.0 V		V _{DD} = 1.05 V			
Parameter	Symbol	STD	−1	STD	−1		
Global clock F _{MAX}	F _{MAXG}					MHz	
Regional clock F _{MAX}	F _{MAXR}					MHz	
Global clock skew	F _{SKEWG}					ps	
Regional clock skew	F _{SKEWR}					ps	
Global clock duty cycle distortion	T _{DCD}					ps	
Regional clock duty cycle distortion	T _{DCD}					ps	

		Temperature Range: −40 °C to 100 °C				Unit	Condition
		V _{DD} = 1.0 V		V _{DD} = 1.05 V			
Parameter	Symbol	STD	−1	STD	−1		
Global clock F _{MAX}	F _{MAXG}					MHz	
Regional clock F _{MAX}	F _{MAXR}					MHz	
Global clock skew	F _{SKEWG}					ps	
Regional clock skew	F _{SKEWR}					ps	
Global clock duty cycle distortion	T _{DCD}					ps	
Regional clock duty cycle distortion	T _{DCD}					ps	

Table 37 • High-Speed I/O Clock Characteristics

		Temperature Range: 0 °C to 100 °C					
		V _{DD} = 1.0 V		V _{DD} = 1.05 V			
Parameter	Symbol	STD	–1	STD	–1	Unit	Condition
High-speed I/O clock F _{MAX}	F _{MAXB}	1000	1250	1000	1250	MHz	HSIO without bridging
		1000	1250	1000	1250	MHz	HSIO with bridging
		1000	1250	1000	1250	MHz	GPIO without bridging
		1000	1250	1000	1250	MHz	GPIO with bridging
High-speed I/O clock skew	F _{SKEWB}	40	30	40	30	ps	HSIO without bridging
		900	700	800	600	ps	HSIO with bridging
		60	60	60	60	ps	GPIO without bridging
		900	700	800	600	ps	GPIO with bridging

Table 37 • High-Speed I/O Clock Characteristics (continued)

		Temperature Range: 0 °C to 100 °C					
		V _{DD} = 1.0 V		V _{DD} = 1.05 V			
Parameter	Symbol	STD	–1	STD	–1	Unit	Condition
High-speed I/O clock duty cycle distortion	T _{DCB}	60	60	60	60	ps	HSIO without bridging
		60	60	60	60	ps	HSIO with bridging
		60	60	60	60	ps	GPIO without bridging
		60	60	60	60	ps	GPIO with bridging
		Temperature Range: –40 °C to 100 °C					
		V _{DD} = 1.0 V		V _{DD} = 1.05 V			
Parameter	Symbol	STD	–1	STD	–1	Unit	Condition
High-speed I/O clock F _{MAX}	F _{MAXB}	1000	1250	1000	1250	MHz	HSIO without bridging
		1000	1250	1000	1250	MHz	HSIO with bridging
		1000	1250	1000	1250	MHz	GPIO without bridging
		1000	1250	1000	1250	MHz	GPIO with bridging
High-speed I/O clock skew	F _{SKEWB}	40	30	40	30	ps	HSIO without bridging
		1000	700	800	600	ps	HSIO with bridging
		60	60	60	60	ps	GPIO without bridging
		1000	700	800	600	ps	GPIO with bridging
High-speed I/O clock duty cycle distortion	T _{DCB}	60	60	60	60	ps	HSIO without bridging
		60	60	60	60	ps	HSIO with bridging
		60	60	60	60	ps	GPIO without bridging
		60	60	60	60	ps	GPIO with bridging

2.6.2.2 PLL

Table 38 • PLL Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Input clock frequency (integer mode)	F _{INI}	1		1250	MHz
Input clock frequency (fractional mode)	F _{INF}	10		1250	MHz
Minimum reference or feedback pulse width ¹	F _{INPULSE}	200			ps
Frequency at the Frequency Phase Detector (PFD) (integer mode)	F _{PHDETI}	1		312	MHz
Frequency at the PFD (fractional mode)	F _{PHDETF}	10		250	MHz
Allowable input duty cycle	F _{INDUTY}	25		75	%

Table 38 • PLL Electrical Characteristics (continued)

Parameter	Symbol	Min	Typ	Max	Unit
Maximum input period clock jitter (reference and feedback clocks) ²	F _{MAXINJ}		120	1000	ps
PLL VCO frequency	F _{VCO}	800		5000	MHz
Low PLL bandwidth	F _{BW}	F _{PHDET} /25		F _{PHDET} /15	MHz
High PLL bandwidth ³	F _{BW}	F _{PHDET} /50		F _{PHDET} /25	MHz
Static phase offset of the PLL outputs ⁴	T _{SPO}	–60		60	ps
	T _{OUTJITTER}				ps
PLL output duty cycle precision	T _{OUTDUTY}	48.5		51.5	%
PLL lock time ⁵	T _{LOCK}		375	625	Cycles
PLL unlock time ⁶	T _{UNLOCK}	2		LOCKCOUNT/4	PFD cycles
PLL output frequency	F _{OUT}	0.050		1250	MHz
Minimum reset pulse width	T _{MRPW}				uS
Maximum delay in the feedback path ⁷	F _{MAXDFB}			1.5	PFD cycles
Spread spectrum modulation spread ⁸	Mod_Spread	0.1		3.1	%
Spread spectrum modulation frequency ⁹	Mod_Freq	F _{PHDET} F/(128)	32	F _{PHDET} F/(128 × 63)	KHz

1. Minimum time for high or low pulse width.
2. Maximum jitter the PLL can tolerate without losing Lock.
3. Medium PLL bandwidth keeps the rest of the line blank.
4. Maximum (± 3 -Sigma) phase error between any two outputs with nominally aligned phases.
5. Input clock cycle is REFDIV/F_{REF}. For example, F_{REF} = 25 MHz, REFDIV = 1, Lock time = 10.0 (assumes LOCKCOUNTSEL setting = 4'd8 (256 cycles)).
6. Unlock occurs if two cycle slip within LOCKCOUNT/4 PFD cycles.
7. Maximum propagation delay of external feedback path in deskew mode.
8. Programmable capability for depth of down spread or center spread modulation.
9. Programmable modulation rate based on the modulation divider setting (1 to 63).

2.6.2.3 DLL

Table 39 • DLL Electrical Characteristics¹

Parameter	Symbol	Min	Typ	Max	Unit
Input reference clock frequency	F _{INF}	133		800	MHz
Input feedback clock frequency	F _{INFDBF}	133		800	MHz
Primary output clock frequency	F _{OUTPF}	133		800	MHz
Secondary output clock frequency ²	F _{OUTSF}	33.3		800	MHz
Input clock jitter ³	F _{INJ}			200	ps
Output clock period jitter (w/clean input) ³	T _{OUTJITTERP}			300	ps
Output clock-to-clock skew between two outputs with the same phase settings	T _{SKEW}			200	ps
DLL lock time ⁴	T _{LOCK}	16		16K	cycles
Minimum reset pulse width	T _{MRPW}	3			ns
Minimum input pulse width ⁵	T _{MIPW}	20			ns
Minimum clock pulse width high ⁶	T _{MPWH}	400			ps
Minimum clock pulse width low ⁶	T _{MPWL}	400			ps
Delay step size	T _{DEL}	14	25	36	ps
Maximum delay block delay ⁷	T _{DELMAX}	2.3	4	6.1	ns
Output clock duty cycle (w/ 50% duty cycle input) ⁸	T _{DUTY}	40		60	%
Output clock duty cycle (in phase reference mode) ⁸	T _{DUTY50}	45		55	%

1. For all DLL modes.
2. CLKOS divided by 4 option.
3. Cycle-to-cycle jitter.
4. Number of reference clock cycles.
5. On load, direction, move, hold, and update input signals.
6. On clock input.
7. 128 delay taps in one delay block.
8. Without duty cycle correction enabled.

2.6.2.4 RC Oscillators

The following tables provide internal RC clock resources for user designs and additional information about designing systems with RF front ends information about emitters generated on chip to support programming operations.

Table 40 • 2 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC _{2FREQ}		2		MHz
Accuracy	RC _{2FACC}	−4		4	%
Duty cycle	RC _{2DC}	48		51	%
Peak-to-peak output period jitter	RC _{2PJIT}	600		900	ps
Peak-to-peak output cycle-to-cycle jitter	RC _{2CJIT}	100		250	ps
Operating current (V _{DD25})	RC _{2IVPPA}			48	μA
Operating current (V _{DD18})	RC _{2IVPP}			0	μA
Operating current (V _{DD})	RC _{2IVDD}			2.6	μA

Table 41 • 160 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC _{SCFREQ}		160		MHz
Accuracy	RC _{SCFACC}	−4		4	%
Duty cycle	RC _{SCDC}	47		52	%
Peak-to-peak output period jitter	RC _{SCPJIT}	130		600	ps
Peak-to-peak output cycle-to-cycle jitter	RC _{SCCJIT}	60		172	ps
Operating current (V _{DD25})	RC _{SCVPPA}			599	μA
Operating current (V _{DD18})	RC _{SCVPP}			0.1	μA
Operating current (V _{DD})	RC _{SCVDD}			60.7	μA

2.6.3 Fabric Specifications

2.6.3.1 Math Blocks

Table 42 • Math Block Performance Extended Commercial Range

Parameter	Symbol	Modes	0 °C to 100 °C			
			V _{DD} = 1.0 V		V _{DD} = 1.05 V	
			STD	–1	STD	–1
Maximum operating frequency	F _{MAX}	18 × 18 multiplication	370	470	440	545
		18 × 18 multiplication summed with 48-bit input	370	470	440	545
		18 × 19 multiplier pre-adder ROM mode	365	465	435	540
		Two 9 × 9 multiplication	370	470	440	545
		9 × 9 Dot Product (DOTP)	370	470	440	545
		Complex 18 × 19 multiplication	360	455	430	530

Table 43 • Math Block Performance Industrial Range

Parameter	Symbol	Modes	–40 °C to 100 °C			
			V _{DD} = 1.0 V		V _{DD} = 1.05 V	
			STD	–1	STD	–1
Maximum operating frequency	F _{MAX}	18 × 18 multiplication	365	465	435	545
		18 × 18 multiplication summed with 48-bit input	365	465	435	545
		18 × 19 multiplier pre-adder ROM mode	355	460	430	540
		Two 9 × 9 multiplication	365	465	435	545
		9 × 9 DOTP	365	465	435	545
		Complex 18 × 19 multiplication	350	450	425	530

2.6.3.2 LSRAM Blocks

Table 44 • LSRAM Performance Extended Commercial Temperature Range

Parameter	0 °C to 100 °C				Unit	Condition
	V _{DD} = 1.0 V		V _{DD} = 1.05 V			
	STD	–1	STD	–1		
Operating frequency	342	428	342	428	MHz	Two-port, all supported widths, pipelined, simple-write, and write-feed-through
	309	428	309	428	MHz	Two-port, all supported widths, non-pipelined, simple-write, and write-feed-through
	342	428	342	428	MHz	Dual-port, all supported widths, pipelined, simple-write, and write-feed-through
	309	428	309	428	MHz	Dual-port, all supported widths, non-pipelined, simple-write, and write-feed-through
	343	428	343	428	MHz	Two-port pipelined ECC mode, pipelined, simple-write, and write-feed-through
	279	295	279	295	MHz	Two-port non-pipelined ECC mode, pipelined, simple-write, and write-feed-through
	343	428	343	428	MHz	Two-port pipelined ECC mode, non-pipelined, simple-write, and write-feed-through
	196	285	196	285	MHz	Two-port non-pipelined ECC mode, non-pipelined, simple-write, and write-feed-through
	274	285	274	285	MHz	Two-port, all supported widths, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port, all supported widths, non-pipelined, and read-before-write
	274	285	274	285	MHz	Dual-port, all supported widths, pipelined, and read-before-write
	274	285	274	285	MHz	Dual-port, all supported widths, non-pipelined, and read-before-write
	274	285	274	285	MHz	Two-port pipelined ECC mode, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port non-pipelined ECC mode, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port pipelined ECC mode, non-pipelined, and read-before-write
	193	285	193	285	MHz	Two-port non-pipelined ECC mode, non-pipelined, and read-before-write

Table 45 • LSRAM Performance Industrial Temperature Range

Parameter	–40°C to 100°C				Unit	Condition
	V _{DD} = 1.0 V		V _{DD} = 1.05 V			
	STD	–1	STD	–1		
Operating frequency	342	428	342	428	MHz	Two-port, all supported widths, pipelined, simple-write, and write-feed-through
	309	428	309	428	MHz	Two-port, all supported widths, non-pipelined, simple-write, and write-feed-through
	342	428	342	428	MHz	Dual-port, all supported widths, pipelined, simple-write, and write-feed-through
	309	428	309	428	MHz	Dual-port, all supported widths, non-pipelined, simple-write, and write-feed-through
	343	428	343	428	MHz	Two-port pipelined ECC mode, pipelined, simple-write, and write-feed-through
	279	295	279	295	MHz	Two-port non-pipelined ECC mode, pipelined, simple-write, and write-feed-through
	343	428	343	428	MHz	Two-port pipelined ECC mode, non-pipelined, simple-write, and write-feed-through
	196	285	196	285	MHz	Two-port non-pipelined ECC mode, non-pipelined, simple-write, and write-feed-through
	274	285	274	285	MHz	Two-port, all supported widths, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port, all supported widths, non-pipelined, and read-before-write
	274	285	274	285	MHz	Dual-port, all supported widths, pipelined, and read-before-write
	274	285	274	285	MHz	Dual-port, all supported widths, non-pipelined, and read-before-write
	274	285	274	285	MHz	Two-port pipelined ECC mode, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port non-pipelined ECC mode, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port pipelined ECC mode, non-pipelined, and read-before-write
	193	285	193	285	MHz	Two-port non-pipelined ECC mode, non-pipelined, and read-before-write

2.6.3.3 μ SRAM Blocks

Table 46 • μ SRAM Performance

Parameter	Symbol	V _{DD} = 1.0 V		V _{DD} = 1.05 V		Unit	Condition
		STD	–1	STD	–1		
Operating frequency	F _{MAX}	400	415	450	480	MHz	Write-port
Read access time	T _{ac}		2		2	ns	Read-port

2.6.3.4 μ PROM

Table 47 • μ PROM Performance

Parameter	Symbol	V _{DD} = 1.0 V		V _{DD} = 1.05 V		Unit
		STD	–1	STD	–1	
Read access time	Tac	10	10	10	10	ns

2.6.4 Transceiver Switching Characteristics

This section describes transceiver switching characteristics.

2.6.4.1 Transceiver Performance

Table 48 • PolarFire Transceiver and TXPLL Performance

Parameter	Symbol	STD			–1			Unit
		Min	Typ	Max	Min	Typ	Max	
Tx data rate ¹	F _{TXRate}	0.25		10.3125	0.25		12.7	Gbps
Tx OOB (serializer bypass) data rate	F _{TXRateOOB}	DC		1.5	DC		1.5	Gbps
Rx data rate when AC coupled	F _{RxRateAC}	0.25		10.3125	0.25		12.7	Gbps
Rx data rate when DC coupled	F _{RxRateDC}	0.25		3.2	0.25		3.2	Gbps
Rx OOB (deserializer bypass) data rate	F _{TXRateOOB}	DC		1.25	DC		1.25	Gbps
TXPLL output frequency ²	F _{TXPLL}	1.6		6.35	1.6		6.35	GHz

1. The reference clock is required to be a minimum of 75 MHz for data rates of 10 Gbps and above.
2. The Tx PLL rate is between 0.5x to 5.5x. The Tx data rate depends on per XCVR lane Tx post-divider settings.

2.6.4.2 Transceiver Reference Clock Performance

Table 49 • PolarFire Transceiver Reference Clock AC Requirements

Parameter	Symbol	STD			–1			Unit
		Min	Typ	Max	Min	Typ	Max	
Reference clock input rate ^{1, 2}	F _{TXREFCLK}	20		800	20		800	MHz
Reference clock input rate ^{1, 2, 3}	F _{XCVRREFCLKMAX CASCADE}	20			20			MHz
Reference clock rate at the PFD ⁴	F _{TXREFCLKPFD}	20		156	20		156	MHz
Reference clock rate recommended at the PFD for Tx rates 10 Gbps and above ⁴	F _{TXREFCLKPFD10G}	75		156	75		156	MHz
Tx reference clock phase noise requirements to meet jitter specifications (622 MHz clock at reference clock input) ⁵								
Phase noise at 1 KHz	F _{TXREFPN}			–105			–105	dBc/Hz
Phase noise at 10 KHz				–110			–110	dBc/Hz
Phase noise at 100 KHz				–115			–115	dBc/Hz
Phase noise at 1 MHz				–135			–135	dBc/Hz
Reference clock input rise time (10%–90%)	T _{REFRISE}		200	500		200	500	ps
Reference clock input fall time (90%–10%)	T _{REFFALL}		200	500		200	500	ps
Reference clock duty cycle	T _{REFDUTY}	40		60	40		60	%
Spread spectrum modulation spread ⁶	Mod_Spread	0.1		3.1	0.1		3.1	%
Spread spectrum modulation frequency ⁷	Mod_Freq	F _{PHDETf} /(128)	32	F _{PHDETf} /(128 × 63)	F _{PHDETf} /(128)	32	F _{PHDETf} /(128 × 63)	KHz

1. See the maximum reference clock rate allowed per input buffer standard.
2. The minimum value applies to this clock when used as an XCVR reference clock. It does not apply when used as a non-XCVR input buffer (DC input allowed).
3. Cascaded reference clock.
4. After reference clock input divider.
5. Required maximum phase noise is scaled based on actual F_{TxRefClk} value by 20 × log10 (TxRefClk/622 MHz).
6. Programmable capability for depth of down-spread or center-spread modulation.
7. Programmable modulation rate based on the modulation divider setting (1 to 63).

2.6.4.3 Transceiver Reference Clock I/O Standards

Table 50 • Transceiver Differential Reference Clock I/O Standards

Differential DC Input Levels										
I/O Standard	V _{DDI}		V _{ICM} ¹				V _{ID} ²			Unit
	Min	Typ	Max	Min	Typ	Max ³	Min	Typ	Max	
LVDS25	2.375	2.500	2.625	0.05	1.25	2.35	0.1	0.35	0.6	V
HCSL25 (for PCIe)	2.375	2.500	2.625	0.05	0.35	2.35	0.1	0.55	1.1	V

1. V_{ICM} is the input common mode.
2. V_{ID} is the input differential voltage.
3. V_{ICM} must be less than V_{DD_XCVR_CLK} – .3 V.

Note: The transceiver reference clock differential receiver supports V_{CM} common mode.

Note: The maximum signal range into the reference clock input buffer for optimal performance is defined as $V_{IHMAX} = V_{CM} + 0.5 V_{ID} < V_{DD_XCVR_CLK}$ and V_{ILMIN} must be $> 0 V$.

2.6.4.4 Transceiver Interface Performance

Table 51 • Transceiver Single-Ended Reference Clock I/O Standards

I/O Standard	V_{DDI}			V_{ICM}^1		V_{ID}^2		Unit
	Min	Typ	Max	Min	Max	Min	Max	
SSTL18I ¹	1.71	1.8	1.89	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	1.89	V
LVC MOS25	2.375	2.5	2.625	-0.3	0.7	1.7	2.625	V

2.6.4.5 Transmitter Performance

Table 52 • Transceiver Reference Clock Input Termination

Parameter	Symbol	Min	Typ	Max	Unit
Single-ended termination	RefTerm		50		Ω
			75		Ω
			150		Ω
Differential termination	RefDiffTerm		100		Ω
Power-up termination			> 50K		Ω

Table 53 • PolarFire Transceiver User Interface Clocks

Parameter	Modes ¹	STD		-1		Unit
		Min	Max	Min	Max	
Transceiver TX_CLK range (non-deterministic PCS mode with global or regional fabric clocks)	8-bit, max data rate = 1.6 Gbps		200		200	MHz
	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 4.8 Gbps		300		300	MHz
	20-bit, max data rate = 6.0 Gbps		300		300	MHz
	32-bit, max data rate = 10.3125 Gbps		325		325	MHz
	40-bit, max data rate = 12.7 Gbps				320	MHz
	64-bit, max data rate = 12.7 Gbps				200	MHz
	80-bit, max data rate = 12.7 Gbps				162.5	MHz
	Fabric pipe mode 32-bit, max data rate = 6.0 Gbps		150		150	MHz

Table 53 • PolarFire Transceiver User Interface Clocks

Parameter	Modes ¹	STD		–1		Unit
		Min	Max	Min	Max	
Transceiver RX_CLK range (non-deterministic PCS mode with global or regional fabric clocks)	8-bit, max data rate = 1.6 Gbps	200		200		MHz
	10-bit, max data rate = 1.6 Gbps	160		160		MHz
	16-bit, max data rate = 4.8 Gbps	300		300		MHz
	20-bit, max data rate = 6.0 Gbps	300		300		MHz
	32-bit, max data rate = 10.3125 Gbps	325		325		MHz
	40-bit, max data rate = 12.7 Gbps			320		MHz
	64-bit, max data rate = 12.7 Gbps			200		MHz
	80-bit, max data rate = 12.7 Gbps			162.5		MHz
	Fabric pipe mode 32-bit, max data rate = 6.0 Gbps	150		150		MHz
Transceiver TX_CLK range (deterministic PCS mode with regional fabric clocks)	8-bit, max data rate = 1.6 Gbps	200		200		MHz
	10-bit, max data rate = 1.6 Gbps	160		160		MHz
	16-bit, max data rate = 4.8 Gbps	300		300		MHz
	20-bit, max data rate = 6.0 Gbps	300		300		MHz
	32-bit, max data rate = 10.3125 Gbps	325		325		MHz
	40-bit, max data rate = 12.7 Gbps			320		MHz
	64-bit, max data rate = 12.7 Gbps			200		MHz
	80-bit, max data rate = 12.7 Gbps			160		MHz
Transceiver RX_CLK range (deterministic PCS mode with regional fabric clocks)	8-bit, max data rate = 1.6 Gbps	200		200		MHz
	10-bit, max data rate = 1.6 Gbps	160		160		MHz
	16-bit, max data rate = 4.8 Gbps	300		300		MHz
	20-bit, max data rate = 6.0 Gbps	300		300		MHz
	32-bit, max data rate = 10.3125 Gbps	325		325		MHz
	40-bit, max data rate = 12.7 Gbps			320		MHz
	64-bit, max data rate = 12.7 Gbps			200		MHz
	80-bit, max data rate = 12.7 Gbps			160		MHz

1. Until specified, all modes are non-deterministic. For more information, see [UG0677: PolarFire FPGA Transceiver User Guide](#).

Table 54 • PolarFire Transceiver Transmitter Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Differential termination	V_{OTERM}	68	85	102	Ω	50K Ω power-up
		80	100	120	Ω	
		120	150	180	Ω	
Common mode voltage ¹	V_{OCM}		$0.525 \times V_{DDA}$		V	DC coupled 50% setting
			$0.6 \times V_{DDA}$		V	DC coupled 60% setting
			$0.7 \times V_{DDA}$		V	DC coupled 70% setting
			$0.8 \times V_{DDA}$		V	DC coupled 80% setting
Rise time ²	T_{TxRF}	20		40	ps	20% to 80%
Fall time ²		20		40	ps	80% to 20%
Differential peak-to-peak amplitude ³	V_{ODPP}	100		1350	mV	Minimum to maximum settings
			1000		mV	1000 mV setting
			800		mV	800 mV setting
			600		mV	600 mV setting
			500		mV	500 mV setting
			400		mV	400 mV setting
			300		mV	300 mV setting
			200		mV	200 mV setting
			100		mV	100 mV setting
Transmit lane P to N skew ⁴	T_{OSKEW}			20	ps	
Lane to lane transmit skew ^{5, 6, 7}	T_{LLSKEW}			200	ps	Single PLL
					ps	Multiple PLL
Electrical idle transition entry time ⁸	$T_{TxEITrEntry}$				ns	
Electrical idle transition exit time ⁸	$T_{TxEITrExit}$				ns	
Electrical idle amplitude	V_{TxElpp}			15	mV	
TXPLL lock time	T_{Lock}				REFCLK UIs	
Digital PLL lock time ⁹	$T_{DPLLlock}$			15K	REFCLK UIs	For Tx jitter cleaner applications
Total jitter ^{10, 11, 12}	T_J				UI	Rate = >8.5 Gbps to 12.7 Gbps
Deterministic jitter ^{10, 11, 12}	T_{DJ}				UI	Tx V_{CO} rate 4.25 GHz to 6.35 GHz
Total jitter ^{10, 11, 12}	T_J				UI	Rate = >3.2 Gbps to 8.5 Gbps
Deterministic jitter ^{10, 11, 12}	T_{DJ}				UI	Tx V_{CO} rate 2.5 GHz to 5.0 GHz

Table 54 • PolarFire Transceiver Transmitter Characteristics (continued)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Total jitter ^{10, 11, 12}	T _J				UI	Rate = >1.6 Gbps to 3.2 Gbps Tx V _{CO} rate 2.5 GHz to 5.0 GHz
Deterministic jitter ^{10, 11, 12}	T _{DJ}				UI	
Total jitter ^{10, 11, 12}	T _J				UI	Rate = >800 Mb/s to 1.6 Gbps Tx V _{CO} rate 2.5 GHz to 5.0 GHz
Deterministic jitter ^{10, 11, 12}	T _{DJ}				UI	
Total Jitter ^{10, 11, 12}	T _J				UI	Rate = 250 Mb/s to 800 Mb/s Tx V _{CO} rate 2.5 GHz to 5.0 GHz
Deterministic jitter ^{10, 11, 12}	T _{DJ}				UI	
Additional Total jitter in Frac mode ¹³	T _{JFRAC}				UI	
Additional deterministic jitter in Frac mode ¹³	T _{DJFRAC}				UI	

1. Increased DC common mode settings above 50% reduce allowed V_{OD} output swing capabilities.
2. Adjustable via transmit emphasis.
3. V_{DDA} = 1.0 V ± 30 mV.
4. With estimated package differences.
5. Single PLL applies to all four lanes in the same quad location with the same TxPLL.
6. Multiple PLL applies to N lanes using multiple TxPLLs from different quad locations.
7. For more information about how to transmit align multiple lanes from different quad locations, see [UG0677: PolarFire FPGA Transceiver User Guide](#).
8. From the PMA mode, the TX_ELEC_IDLE port to the XCVR TXP/N pins.
9. FTxRefClk = 75 MHz with typical settings.
10. Jitter measurements are obtained using the TXPL_SSC and/or TXPLL in integer mode with the slowest possible V_{CO} rate with a reference clock of at least 100 MHz that meets the input phase noise specifications.
11. Improved jitter characteristics for a specific industry standard are possible in many cases due to improved reference clock or higher V_{CO} rate used.
12. Tx jitter is specified with all transmitters on the device enabled, a 10-12 bit error rate (BER) and Tx data pattern of PRBS2⁷.
13. Additional T_J when Fractional-N mode is enabled.

2.6.4.6 Receiver Performance

Table 55 • PolarFire Transceiver Receiver Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Input voltage range	V_{IN}	0		$V_{DDA} + 0.3$	V	
Differential peak-to-peak amplitude	V_{IDPP}	140		1250	mV	
Differential termination	V_{ITERM}	68	85	102	Ω	50K Ω power-up
		80	100	120	Ω	
		120	150	180	Ω	
Common mode voltage	V_{ICMAC}		$1.0 \times V_{DDA}$		V	AC coupled
	V_{ICMDC}^1	$0.7 \times V_{DDA}$		$0.9 \times V_{DDA}$	V	DC coupled
Electrical idle detect threshold (differential)	V_{EIDET}	60		300	mV	
Exit electrical idle detection time	T_{EIDET}		50	100	ns	
Run length of consecutive identical digits (CID)	C_{ID}			85	UI	
CDR PPM tolerance ²	C_{DRPPM}			1.15	% UI	
CDR lock-to-data time	T_{LTD}		512		CDR_{REFCLK} UIs	
CDR lock-to-ref time	T_{LTF}	512		1024	CDR_{REFCLK} UIs	
Loss-of-signal detect threshold - Low	V_{DETLow}			65 ³	mV	Setting = PCIe
				75 ⁴	mV	Setting = SATA
						Setting = 1
						Setting = 2
						Setting = 3
						Setting = 4
						Setting = 5
						Setting = 6
Loss-of-signal detect threshold - High	$V_{DETHIGH}$	175 ⁴			mV	Setting = PCIe
		200 ⁴			mV	Setting = SATA
						Setting = 1
						Setting = 2
						Setting = 3
						Setting = 4
						Setting = 5
						Setting = 6
						Setting = 7

Table 55 • PolarFire Transceiver Receiver Characteristics (continued)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Sinusoidal jitter tolerance	T_{SJTOL}				UI	>8.5 - 12.7 Gbps ⁴
					UI	>3.2 - 8.5 Gbps ⁵
					UI	>1.6 to 3.2 Gbps ⁵
					UI	>0.8 to 1.6 Gbps ⁶
					UI	250 to 800 Mbps ⁶
Total jitter tolerance with stressed eye	$T_{TJTOLSE}$				UI	3.125 Gbps ⁵
					UI	6.25 Gbps ⁵
					UI	10.3125 Gbps ⁵
					UI	12.5 Gbps ⁵
Sinusoidal jitter tolerance with stressed eye	$T_{SJTOLSE}$				UI	3.125 Gbps ⁵
					UI	6.25 Gbps ⁵
					UI	10.3125 Gbps ⁵
					UI	12.5 Gbps ⁵
CTLE DC gain (all stages, max settings)				10	dB	
CTLE AC gain all stages, max settings)				16	dB	
DFE AC gain (per 5 stages, max settings)				14	dB	
CTLE auto adaptive calibration time					us	
CTLE + DFE auto adaptive calibration time					us	

- Valid at 3.2 Gbps and below.
- Data vs. Rx reference clock frequency.
- Achieves compliance with PCIe electrical idle detection.
- Rx jitter values based on bit error ratio (BER) of 10⁻¹², AC coupled input with 400 mV V_{ID} , single stage of Rx CTLE enabled, DFE disabled, 80 MHz sinusoidal jitter injected to Rx data.
- Rx jitter values based on BER of 10⁻¹², AC coupled input with 400 mV V_{ID} , Rx CTLE disabled, DFE disabled, 80 MHz sinusoidal jitter injected to Rx data.

2.6.5 Transceiver Protocol Characteristics

2.6.5.1 PCI Express

Table 56 • PCI Express

	Data Rate	Min	Max	Unit
PCIe Gen1				
Total transmit jitter	2.5 Gbps			UI
Receiver jitter tolerance	2.5 Gbps			UI
PCIe Gen2				
Total transmit jitter	5.0 Gbps			UI
Receiver jitter tolerance	5.0 Gbps			UI

2.6.5.2 10GbE (XAUI, RXAUI, 10GBASE-R, and 10GBASE-KR)

Table 57 • 10GbE (XAUI, RXAUI, 10GBASE-R, and 10GBASE-KR)

	Data Rate	Min	Max	Unit
XAUI				
Total transmit jitter	3.125 Gbps			UI
Receiver jitter tolerance	3.125 Gbps			UI
RXAUI				
Total transmit jitter	6.25 Gbps			UI
Receiver jitter tolerance	6.25 Gbps			UI
10GBASE-R				
Total transmit jitter	10.3125 Gbps			UI
Receiver jitter tolerance	10.3125 Gbps			UI
10GBASE-KR				
Total transmit jitter	10.3125 Gbps			UI
Receiver jitter tolerance	10.3125 Gbps			UI
10GBASE-KR w/ FEC				
Total transmit jitter	12.5 Gbps			UI
Receiver jitter tolerance	12.5 Gbps			UI

2.6.5.3 1GbE (SGMII, 1000BASE-T, 1000BASE-X, and QSGMII)

Table 58 • 1GbE (SGMII, 1000BASE-T, 1000BASE-X, and QSGMII)

	Data Rate	Min	Max	Unit
SGMII				
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI
1000BASE-T				
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI
1000BASE-X				
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI
QSGMII				
Total transmit jitter	5.0 Gbps			UI
Receiver jitter tolerance	5.0 Gbps			UI

2.6.5.4 CPRI

Table 59 • CPRI

	Data Rate	Min	Max	Unit
Total transmit jitter	0.6144 Gbps			UI
	1.2288 Gbps			UI
	2.4576 Gbps			UI
	3.0720 Gbps			UI
	4.9152 Gbps			UI
	6.1440 Gbps			UI
	9.8304 Gbps			UI
	10.1376 Gbps			UI
	12.16512 Gbps			UI
Receive jitter tolerance	0.6144 Gbps			UI
	1.2288 Gbps			UI
	2.4576 Gbps			UI
	3.0720 Gbps			UI
	4.9152 Gbps			UI
	6.1440 Gbps			UI
	9.8304 Gbps			UI
	10.1376 Gbps			UI
	12.16512 Gbps			UI

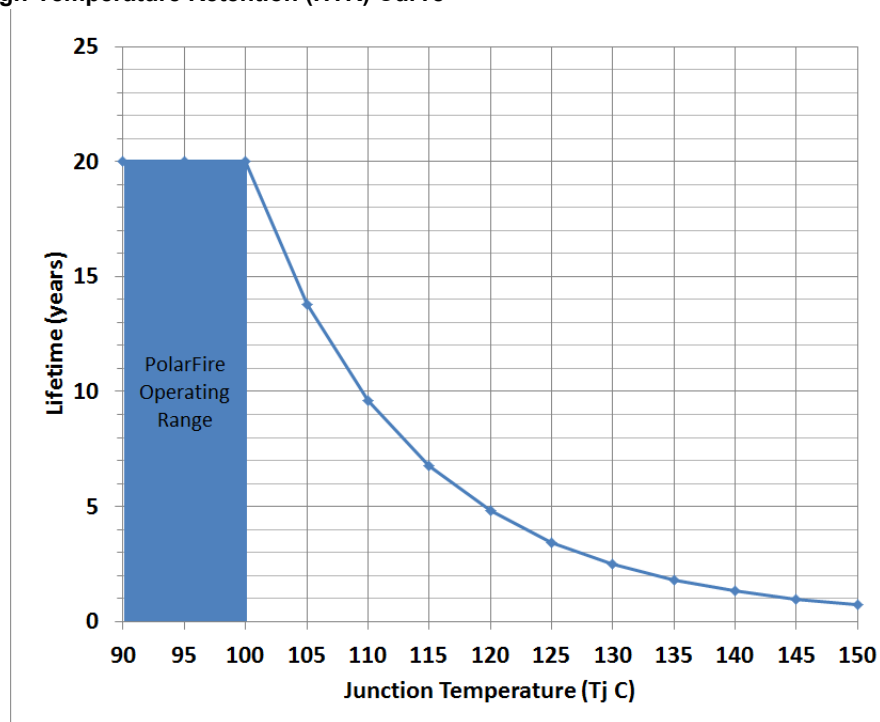
2.6.5.5 JESD204B

Table 60 • JESD204B

	Data Rate	Min	Max	Unit
Total transmit jitter	3.125 Gbps			UI
	6.25 Gbps			UI
	12.5 Gbps			UI
Receive jitter tolerance	3.125 Gbps			UI
	6.25 Gbps			UI
	12.5 Gbps			UI

2.6.6 Non-Volatile Characteristics

Figure 3 • High-Temperature Retention (HTR) Curve



2.6.6.1 FPGA Programming Cycle and Retention

Table 61 • FPGA Programming Cycles Vs Retention Characteristics

Programming T_J	Programming Cycles, Max	Retention Years	Retention Years at T_J
0 °C to 85 °C	1000	20	85 °C
0 °C to 100 °C	500	20	100 °C
–20 °C to 100 °C	500	20	100 °C
–40 °C to 100 °C	500	20	100 °C
–40 °C to 85 °C	1000	16	100 °C
–40 °C to 55 °C	2000	12	100 °C

Note: Power supplied to the device must be valid during programming operations such as programming, verify, zeroization, and digest checks. Programming recovery mode is available only for In-Application Programming mode and requires an external SPI flash.

2.6.6.2 FPGA Programming Time

Table 62 • Master SPI Programming Time (IAP)

Parameter	Symbol	Devices	Typ	Max	Unit
Programming time	T_{PROG}	MPF100T, TL, TS, TLS			s
		MPF200T, TL, TS, TLS	30		s
		MPF300T, TL, TS, TLS	50		s
		MPF500T, TL, TS, TLS	55		s

Table 63 • Slave SPI Programming Time

Parameter	Symbol	Devices	Typ	Max	Unit
Programming time	T_{PROG}	MPF100T, TL, TS, TLS			s
		MPF200T, TL, TS, TLS	35		s
		MPF300T, TL, TS, TLS	58		s
		MPF500T, TL, TS, TLS	63		s

Table 64 • JTAG Programming Time

Parameter	Symbol	Devices	Typ	Max	Unit
Programming time	T_{PROG}	MPF100T, TL, TS, TLS			s
		MPF200T, TL, TS, TLS	35		s
		MPF300T, TL, TS, TLS	58		s
		MPF500T, TL, TS, TLS	63		s

2.6.6.3 FPGA Bitstream Sizes

Table 65 • Bitstream Sizes

Devices	Size		
	.SPI File	.STPL File	Unit
MPF100T, TL, TS, TLS	3.41	5.44	MB
MPF200T, TL, TS, TLS	5.9	9.4	MB
MPF300T, TL, TS, TLS	9.1	14.4	MB
MPF500T, TL, TS, TLS	14.4	22.8	MB

2.6.6.4 Digest Cycles

Digests verify the integrity of the programmed non-volatile data. Digests are a cryptographic hash of various data areas. Any digest that reports back an error raises the digest tamper flag.

Table 66 • Maximum Number of Digest Cycles

Digest T_J	Storage and Operating T_J	Retention Since Programmed. N = Number Digests During that Time ¹							Unit	Retention
		N <= 300	N = 500	N = 1000	N = 1500	N = 2000	N = 4000	N = 6000		
-40 to 100	-40 to 100	20 × LF	17 × LF	12 × LF	10 × LF	8 × LF	4 × LF	2 × LF	°C	Years
-40 to 100	0 to 100	20 × LF	17 × LF	12 × LF	10 × LF	8 × LF	4 × LF	2 × LF	°C	Years
-40 to 85	-40 to 85	20 × LF	20 × LF	20 × LF	20 × LF	16 × LF	8 × LF	4 × LF	°C	Years
-40 to 55	-40 to 55	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	20 × LF	°C	Years

1. LF = Lifetime factor as defined by the number of programming cycles the device has seen under the conditions listed in the following table.

Table 67 • FPGA Programming Cycles Lifetime Factor

Programming T_J	Programming Cycles	LF
-40 °C to 100 °C	500	1
-40 °C to 85 °C	1000	0.8
-40 °C to 55 °C	2000	0.6

Note: The maximum number of device digest cycles is 100K.

Note: Digests are operational only over the -40 °C to 100 °C temperature range.

Note: After a program cycle, an additional N digests cycles are allowed with the resultant retention characteristics for the total operating and storage temperature shown.

Note: Retention is specified for total device storage and operating temperature.

Note: All temperatures are junction temperatures (T_J).

Note: Example 1—500 digests cycles are performed between programming cycles. $N = 500$. The operating conditions are -40°C to 85°C T_J . 501 programming cycles are occurred. The retention under these operating conditions is $20 \times \text{LF} = 20 \times .8 = 16$ years.

Note: Example 2—programming cycle has occurred, $N = 1500$ digest cycles are occurred. Temperature range is -40°C to 100°C . The resultant retention is $10 \times \text{LF}$ or 10 years over the industrial temperature range.

2.6.6.5 Digest Time

Table 68 • Digest Times

Parameter	Devices	Typ	Max	Unit
Setup time	All	2		us
Fabric digest run time	MPF100T, TL, TS, TLS			ms
	MPF200T, TL, TS, TLS	957		ms
	MPF300T, TL, TS, TLS	1451		ms
	MPF500T, TL, TS, TLS	1876		ms
UFS CC digest run time	MPF100T, TL, TS, TLS			us
	MPF200T, TL, TS, TLS	28		us
	MPF300T, TL, TS, TLS	28		us
	MPF500T, TL, TS, TLS	28		us
sNVM digest run time ¹	MPF100T, TL, TS, TLS			ms
	MPF200T, TL, TS, TLS			ms
	MPF300T, TL, TS, TLS			ms
	MPF500T, TL, TS, TLS			ms
UFS UL digest run time	MPF100T, TL, TS, TLS			us
	MPF200T, TL, TS, TLS	41		us
	MPF300T, TL, TS, TLS	41		us
	MPF500T, TL, TS, TLS	41		us
User Key digest run time ²	MPF100T, TL, TS, TLS			us
	MPF200T, TL, TS, TLS	564		us
	MPF300T, TL, TS, TLS	564		us
	MPF500T, TL, TS, TLS	564		us
UFS UPERM digest run time	MPF100T, TL, TS, TLS			us
	MPF200T, TL, TS, TLS	28		us
	MPF300T, TL, TS, TLS	28		us
	MPF500T, TL, TS, TLS	28		us
Factory digest run time	MPF100T, TL, TS, TLS			us
	MPF200T, TL, TS, TLS	461		us
	MPF300T, TL, TS, TLS	461		us
	MPF500T, TL, TS, TLS	461		us

1. The entire sNVM is used as ROM.

2. Valid for User Key 0 through 6.

Note: These times do not include the power-up to functional timing overhead when using digest checks on power-up.

2.6.6.6 Zeroization Time

Table 69 • Zeroization Times for MPF100T, TL, TS, TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}			ms	1 iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1, 3}			ms	1 iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	1 iteration of scrubbing
Time to scrub the fabric data ¹			seconds	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			seconds	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			seconds	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ^{1, 4}			seconds	Full scrubbing
Time to verify ⁵			seconds	

1. Total completion time after interning zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 70 • Zeroization Times for MPF200T, TL, TS, TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}			ms	1 iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1, 3}			ms	1 iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	1 iteration of scrubbing
Time to scrub the fabric data ¹			seconds	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			seconds	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			seconds	Full scrubbing
Time to scrub the fabric data PNVM data (non-recoverable) ^{1, 4}			seconds	Full scrubbing
Time to verify ⁵			seconds	

1. Total completion time after interning zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. non-recoverable mode—zeroizes user design security setting, sNVM and factory keys and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 71 • Zeroization Times for MPF300T, TL, TS, TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization	8.7		ms	Zip flag set
Time to destroy the Fabric data ¹	34.3		ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}	801		ms	1 iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1, 3}	860		ms	1 iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}	909.9		ms	1 iteration of scrubbing
Time to scrub the fabric data ¹	1.151		seconds	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}	2.4		seconds	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}	2.58		seconds	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ^{1, 4}	2.73		seconds	Full scrubbing
Time to verify ⁵	1.57		seconds	

1. Total completion time after interning zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 72 • Zeroization Times for MPF500T, TL, TS, TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization	8.7		ms	Zip flag set
Time to destroy the fabric data ¹	34.3		ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}	801		ms	1 iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1, 3}	860		ms	1 iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}	909.9		ms	1 iteration of scrubbing
Time to scrub the fabric data ¹	1.151		seconds	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}	2.4		seconds	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}	2.58		seconds	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ^{1, 4}	2.73		seconds	Full scrubbing
Time to verify ⁵	1.74		seconds	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys and factory data required for programming.
5. Time to verify after scrubbing completes.

2.6.6.7 Verify Time

Table 73 • Standalone Fabric Verify Times

Parameter	Devices	Typ	Max	Unit
Standalone verification over JTAG	MPF100T, TL, TS, TLS			s
	MPF200T, TL, TS, TLS			s
	MPF300T, TL, TS, TLS			s
	MPF500T, TL, TS, TLS			s
Standalone verification over SPI	MPF100T, TL, TS, TLS			s
	MPF200T, TL, TS, TLS			s
	MPF300T, TL, TS, TLS			s
	MPF500T, TL, TS, TLS			s

Note: Standalone verify is limited to 2000 total device hours over the industrial –40 °C to 100 °C temperature.

Note: Use the digest system service, for verify device time more than 2000 hours.

Note: Standalone verify checks the programming margin on both the P and N gates of the push-pull cell.

Note: Digest checks only the P side of the push-pull gate. However, the push pull gates work in tandem. Digest check is recommended if users believe they will exceed the 2000 hour verify time specification.

Table 74 • Verify Time By Programming Hardware

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor
MPF100T, TL, TS, TLS					
MPF200T, TL, TS, TLS					
MPF300T, TL, TS, TLS		1 min 50 sec	1 min 36 sec		
MPF500T, TL, TS, TLS		2 min 40 sec	2 min 20 sec		

Note: FlashPro4 verification time collected based on 4 MHz TCK.

Note: FlashPro5 verification time collected based on 10 MHz TCK.

2.6.6.8 Secure NVM Performance

Table 75 • sNVM Read/Write Characteristics

Parameter	Min	Typ	Max	Unit	Conditions
Plain text programming				ms	
Authenticated text programming				ms	
Authenticated and encrypted text programming				ms	
Authentication R/W 1st access from power-up overhead				ms	
Plain text read				ms	
Authenticated text read					
Authenticated and decrypted text read				ms	

Note: Page size = 252 Bytes (non-authenticated), 236 Bytes (authenticated)

Note: Only page reads and writes allowed.

Note: $T_{KEYOVHD}$ is an additional time that occurs on the 1st R/W to sNVM using authenticated or authenticated and encrypted text.

2.6.6.9 Secure NVM Programming Cycles

Table 76 • sNVM Programming Cycles Vs Retention Characteristics

Programming Temperature	Programming Cycles Per Page, Max	Programming Cycles Per Block, Max	Retention Years
–40 °C to 100 °C	10,000	100,000	20
–40 °C to 85 °C	10,000	100,000	20
–40 °C to 55 °C	10,000	100,000	20

Note: Page size = 128 Bytes

Note: Block size = 56 KBytes

2.6.7 System Services

This section described system switching and throughput characteristics.

2.6.7.1 System Services Throughput Characteristics

Table 77 • System Services Throughput Characteristics

Parameter	Symbol	Service ID	Typ	Max	Conditions
Serial number	T_{Serial}	00H			
User code	T_{User}	01H			
Design information	T_{Design}	02H			
Device certificate	T_{Cert}	03H			
Read digests	T_{digest_read}	04H			
Query security locks	T_{sec_Query}	05H			
Read debug information	T_{Rd_debug}	06H			
Reserved		07H - 0FH			
Secure NVM write plain text ¹	$T_{SNVM_Wr_Plain}$	10H			
Secure NVM write authenticated plain text ¹	$T_{SNVM_Wr_Auth}$	11H			
Secure NVM write authenticated cipher text ¹	$T_{SNVM_Wr_Cipher}$	12H			
Reserved		13H - 17H			
Secure NVM read ¹	T_{SNVM_Rd}	18H			
Digital signature service raw	T_{SIG_RAW}	19H			
Digital signature service DER	T_{SIG_DER}	1AH			
Reserved		1BH - 1FH			
PUF emulation	$T_{Challenge}$	20H			
Nonce service	T_{Nonce}	21H			
Bitstream authentication	T_{BIT_AUTH}	22H			SPI F_{MAX}
IAP Image authentication	T_{IAP_AUTH}	23H			SPI F_{MAX} + Optional INIT data
Reserved		26H - 3FH			

Table 77 • System Services Throughput Characteristics (continued)

Parameter	Symbol	Service ID	Typ	Max	Conditions
Flash*Freeze service ²	T _{FF}	40H			
Flash*Freeze service with time out ²	T _{FF_TOUT}	41H			
In application programming by index ³	T _{IAP_Prg_Index}	42H			
In application programming by SPI address ³	T _{IAP_Prg_Addr}	43H			
In application verify by index ³	T _{IAP_Ver_Index}	44H			
In application verify by SPI address ³	T _{IAP_Ver_Addr}	45H			
Auto update ³	T _{AutoUpdate}	46H			
Digest check ⁴	T _{digest_chk}	47H			

1. See [Table 75](#), page 58.

2. See [LSRAM and μSRAM Initialization Time](#), page 74.

3. See [FPGA Programming Time](#), page 53.

4. See [Table 68](#), page 55.

2.6.8 User Crypto

2.6.8.1 TeraFire 5200B Switching Characteristics

Table 78 • TeraFire F5200B Switching Characteristics

Parameter	Symbol	V _{DD} = 1.0 V		V _{DD} = 1.05 V		Unit	Condition
		STD	–1	STD	–1		
Operating frequency	F _{MAX}	189		189		MHz	–40 °C to 100 °C

2.6.8.2 TeraFire 5200B Throughput Characteristics

Table 79 • TeraFire F5200B Throughput Characteristics

Algorithm	Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock Cycles Per Message	Clock-Cycles ¹
AES	AES-ECB-128 encrypt ²	128	515	4523
		64K	52157	56148
	AES-ECB-128 decrypt ²	128	561	4558
		64K	52433	56428
	AES-ECB-256 encrypt ²	128	531	4730
		64K	60349	64545
	AES-ECB-256 decrypt ²	128	593	4800
		64K	60721	64930
	AES-CBC-256 encrypt ²	128	592	5366
		64K	62739	67526
	AES-CBC-256 decrypt ²	128	621	5401
		64K	60901	65671
	AES-GCM-128 encrypt ² , 128-bit tag, 128-bit authtag before plaintext (full message encrypted/authenticated)	128	2506	6857
		64K	82188	86517
	AES-GCM-128 encrypt ² , 128-bit tag, (full message encrypted/authenticated)	128	1960	6280
		64K	81642	85975
GMAC	AES-GCM-256 ² , 128-bit tag, (message is only authenticated)	128	2008	6557
		64K	81674	86217
	HMAC-SHA-256 ² , 256-bit key	512	7477	9577
		64K	88367	90462
HMAC	HMAC-SHA-384 ² , 384-bit key	1024	11731	14042
		64K	106111	108402

Table 79 • TeraFire F5200B Throughput Characteristics (continued)

Algorithm	Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock Cycles Per Message	Clock-Cycles ¹
CMAC	AES-CMAC-256 ² (message is only authenticated)	128	223	14924
		64K	223	159942
KEY TREE	128-bit nonce + 8-bit optype (N/A)		102511	105413
	256-bit nonce + 8-bit optype (N/A)		103272	106454
SHA	SHA-1 ²	512	2386	3683
		64K	77576	78863
	SHA-256 ²	512	2516	3823
		64K	84752	86038
	SHA-384 ²	1024	4162	5468
		64K	51274	101543
	SHA-512 ²	1024	4162	5468
		64K	51274	101543
ECC	ECDSA SigGen, P-384/SHA-384 ²	1024	12530673	12538712
		8K	12545812	12553842
	ECDSA SigGen, P-384/SHA-384	1024	5502580	5510607
	ECDSA SigVer, P-384/SHA-384	1024	6329349	6336684
		8K	6374140	6381484
	Key agreement (KAS), P-384 ²		5037644	5043464
	Point multiply, P-256 ²		5176445	5182129
	Point multiply, P-384 ²		12048196	12055249
	Point multiply, P-521 ²		26886848	26895584
	Point addition, P-384		5049697	5056192
	KeyGen (PKG), P-384 ²		12059342	12067938
	KeyVer (PKV), P-384 ²			
	Point verification, P-384		5185	8214

Table 79 • TeraFire F5200B Throughput Characteristics (continued)

Algorithm	Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock Cycles Per Message	Clock-Cycles ¹
IFC (RSA)	Encrypt, RSA-2048, e=65537	2048	1694898	1707983
	Encrypt, RSA-3072, e=65537	3072	3734115	3752628
	Decrypt, RSA-2048 ² , CRT	2048		
	Decrypt, RSA-3072 ² , CRT	3072		
	Decrypt, RSA-4096 ² , CRT	4096		
	Decrypt, RSA-8192 ² , CRT	8192		
	Decrypt, RSA-3072, CRT	3072	38135488	38160269
	SigGen, RSA-3072/ SHA-384 ² , PKCS #1 V 1.5	1024 8K		
	SigGen, RSA-3072/ SHA-384, PKCS #1, V 1.5	1024 8K	13199641 13210656	147436351 147447376
	SigVer, RSA-3072/ SHA-384, e = 65537, PKCS #1 V 1.5	1024 8K	21574887 21583957	88701666 88710731
	SigVer, RSA-2048/ SHA-256, e = 65537, PKCS #1 V 1.5	1024 8K	26916920 26931018	26929701 26943806
	SigGen, RSA-3072/ SHA-384, ANSI X9.31,	1024 8K	13148583 13156661	147385003 147393088
	SigVer, RSA-3072/ SHA-384, e = 65537, ANSI X9.31	1024 8K	21614156 21632391	88740653 88758888
FFC (DH)	SigGen, DSA-3072/ SHA-384 ²	1024 8K	27948851 27961233	27966136 27978526
	SigGen, DSA-3072/ SHA-384	1024	11951377	11967172
	SigVer, DSA-3072/ SHA-384	1024 8K	24484509 24950598	24504278 24970373
	SigVer, DSA-2048/ SHA-256	1024 8K	10016686 10008257	10031188 10022753
	Key Agreement (KAS), DH-3072 (p = 3072, security = 256)		12207595	12225892
	Key Agreement (KAS), DH-3072 (p = 3072, security = 256) ²		40537984	241882971

Table 79 • TeraFire F5200B Throughput Characteristics (continued)

Algorithm	Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock Cycles Per Message	Clock-Cycles ¹
NRBG	Instantiate: strength, s = 256, 384-bit nonce, 384-bit personalization string		0	757
	Reseed: no additional input, s = 256		769	4630
	Reseed: 384-bit additional input, s = 256		1490	6271
	Generate: (no add'l input, no prediction resistance), s = 256	128	1909	3640
		8K	12808	27125
	Generate: (no add'l input), prediction resistance enabled, s = 256	128	6078	7817
		8K	16977	31337
	Generate: 384-bit add'l input, (no prediction resistance), s = 256	128	6064	8539
		8K	16963	32024
	Generate: (no add'l input, no prediction resistance), s = 256	128	7719	10196
		8K	18618	33681
	Un-instantiate		761	1613

1. Total clock-cycles from Cortex-M1 driver to athena TeraFire core completion and return. 100 MHz Cortex-M1 and Athena TeraFire core.
2. With DPA counter measures.

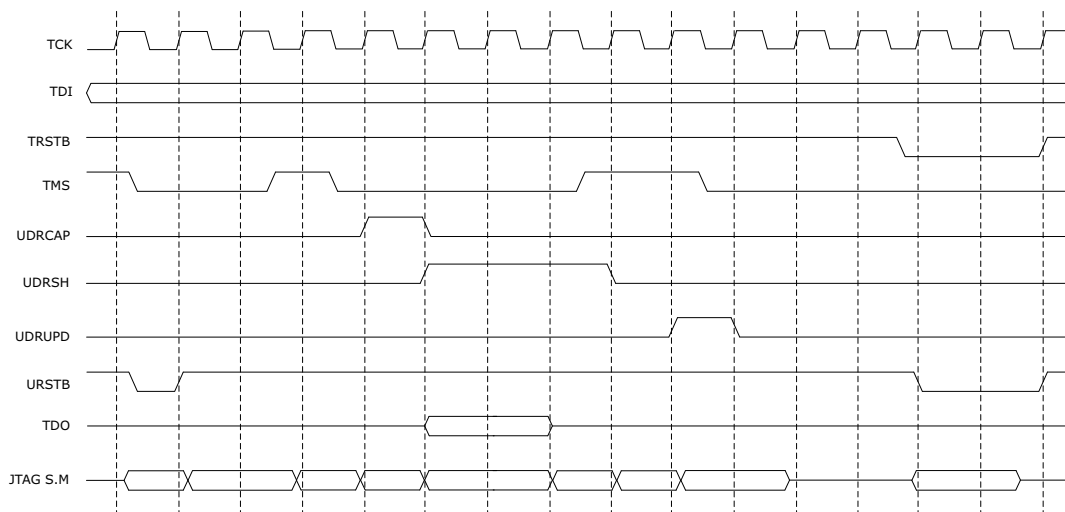
2.6.9 Fabric Macros

This section describes switching characteristics of UJTAG, UJTAG_SEC, USPI, system controller, and temper detectors and dynamic reconfiguration details.

2.6.9.1 UJTAG Switching Characteristics

Table 80 • UJTAG Performance Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
TCK frequency	F _{TCK}			50	MHz	

Figure 4 • UJTAG Timing Diagram

2.6.9.2 UJTAG_SEC Switching Characteristics

Table 81 • UJTAG Security Performance Characteristics

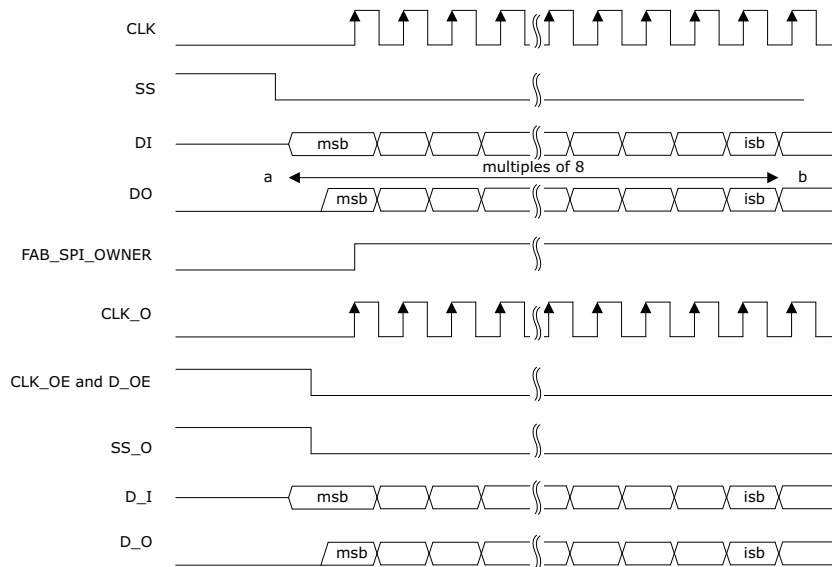
Parameter	Symbol	Min	Typ	Max	Unit	Condition
TCK frequency	F_{TCK}				MHz	

2.6.9.3 USPI Switching Characteristics

Table 82 • SPI Macro Interface Timing Characteristics

Parameter	Symbol	$V_{DDI} = 3.3\text{ V}$	$V_{DDI} = 2.5\text{ V}$	$V_{DDI} = 1.8\text{ V}$	$V_{DDI} = 1.5\text{ V}$	$V_{DDI} = 1.2\text{ V}$	Unit
		Max	Max	Max	Max	Max	
Propagation delay from the fabric to pins ¹	T_{PD_MOSI}	0.8	1	1.2	1.4	1.6	ns
	T_{PD_MISO}	3.5	3.75	4	4.25	4.5	ns
	T_{PD_SS}	3.5	3.75	4	4.25	4.5	ns
	T_{PD_SCK}	3.5	3.75	4	4.25	4.5	ns
	$T_{PD_MOSI_OE}$	3.5	3.75	4	4.25	4.5	ns
	$T_{PD_SS_OE}$	3.5	3.75	4	4.25	4.5	ns
	$T_{PD_SCK_OE}$	3.5	3.75	4	4.25	4.5	ns

1. Assumes CL of the relevant I/O standard as described in the input and output delay measurement tables.

Figure 5 • USPI Switching Characteristics

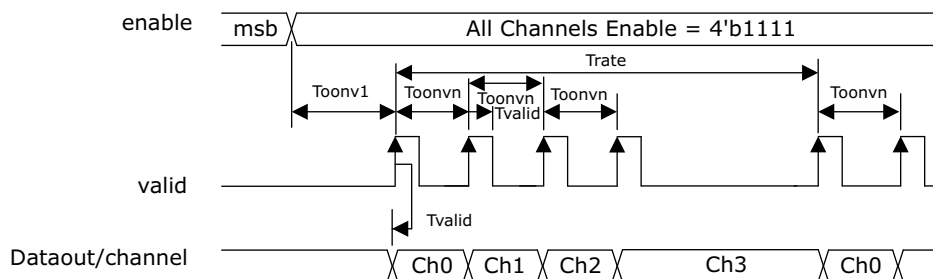
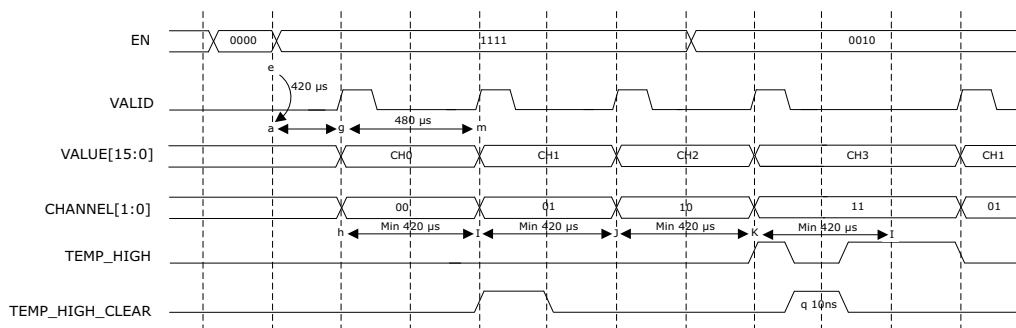
2.6.9.4 Tamper Detectors

Table 83 • ADC Conversion Rate

Parameter	Description	Min	Typ ¹	Max
T _{CONV1}	Time from enable changing from zero to non-zero value to first conversion completes. Minimum value applies when POWEROFF = 0	420 us		470 us
T _{CONVN}	Time between subsequent channel conversion's		480 us	
T _{SETUP}	Data channel and output to valid asserted. Data is held until next conversion completes, that is > 480 us.	0 ns		
T _{VALID} ²	Width of the valid pulse.	1.625 us		2 us
T _{RATE}	Time from start of first set of conversions to the start of the next set. Can be considered as the conversion rate. Is set by the conversion rate parameter	480 us	Rate ×32 us	8128 us

1. Min, typ, and max refer to variation due to functional configuration and the raw TVS value. The actual internal correction time will vary based on the raw TVS value.
2. The pulse width varies depending on the time taken to complete the internal calibration multiplication, this can be up to 375 ns.

Note: Once the TVS block is active, the enable signal is sampled 25 ns before the falling edge of valid. The next enabled channel in the sequence 0-1-2-3 is started, that is if channel 0 has just completed and only channels 0 and 3 enabled; the next channel will be 3. When all the enabled, channels in the sequence 0-1-2-3 are completed; the TVS waits for the conversion rate timer to expire. The enable signal may be changed at any time if it changes to 4'b0000 while valid is asserted (and 25 ns before valid is de-asserted) then no further conversions will be started.

Figure 6 • ADC Switching Characteristics**Figure 7 • ADC Switching Characteristics Timing Diagram****Table 84 • Temperature and Voltage Sensor Electrical Characteristics**

Parameter	Min	Typ	Max	Unit	Condition
Temperature sensing range	-40		125	°C	
Temperature sensing accuracy	-10		10	°C	
Voltage sensing range	0.9		2.8	V	
Voltage sensing accuracy	-1.5		1.5	%	

Table 85 • Tamper Macro Timing Characteristics—Flags and Clearing

Parameter	Symbol	Typ	Max	Unit
From event detection to flag generation	$T_{JTAG_ACTIVE}^{1,2}$		5	ns
	$T_{MESH_ERR}^2$	0.1	6.5	us
	$T_{CLK_GLITCH}^{1,2}$		50	ns
	$T_{CLK_FREQ}^{1,2}$		4	us
	$T_{LOW_1P05}^2$		44	us
	$T_{HIGH_1P8}^2$		44	us
	$T_{HIGH_2P5}^2$		44	us
	$T_{GLITCH_1P05}^2$		20	ns
	$T_{SECDEC}^{1,2}$		5	ns
	$T_{SCB_ERR}^2$		50	ns
	$T_{WDOG}^{1,2}$		5	ns
	$T_{LOCK_ERR}^2$		5	ns

Table 85 • Tamper Macro Timing Characteristics—Flags and Clearing (continued)

Parameter	Symbol	Typ	Max	Unit
Time from system controller instruction execution to flag generation	$T_{INST_BUF_ACCESS}^{2,3}$			
	$T_{INST_DEBUG}^{2,3}$			
	$T_{INST_CHK_DIGEST}^{2,3}$			
	$T_{INST_EC_SETUP}^{2,3}$			
	$T_{INST_FACT_PRIV}^{2,3}$			
	$T_{INST_KEY_VAL}^{2,3}$			
	$T_{INST_MISC}^{2,3}$			
	$T_{INST_PASSCODE_MATCH}^{2,3}$			
	$T_{INST_PASSCODE_SETUP}^{2,3}$			
	$T_{INST_PROG}^{2,3}$			
	$T_{INST_PUB_INFO}^{2,3}$			
	$T_{INST_ZERO_RECO}^{2,3}$			
	$T_{INST_PASSCODE_FAIL}^{2,3}$			
	$T_{INST_KEY_VAL_FAIL}^{2,3}$			
	$T_{INST_UNUSED}^{2,3}$			
Time from sending the CLEAR to deassertion on FLAG	T_{CLEAR_FLAG}		3	ns

1. Not available during Flash*Freeze.
2. The timing does not impact the user design, however it is useful for Security Analysis.
3. System service requests from the fabric will interrupt the system controller delaying the generation of the flag.

Table 86 • Tamper Macro Response Timing Characteristics

Parameter	Symbol	Typ	Max	Unit
Time from triggering the response to all I/Os disabled.	$T_{IO_DISABLE}$		150	ns
Time from negation of RESPONSE to all I/Os re-enabled.	$T_{CLR_IO_DISABLE}$		10	us
Time from triggering the response to security locked.	$T_{LOCKDOWN}$		20	ns
Time from negation of RESPONSE to earlier security unlock condition.	$T_{CLR_LOCKDOWN}$		20	ns
Time from triggering the response to device enters RESET.	T_{tr_RESET}			
Time from triggering the response to start of zeroization.	$T_{tr_ZEROLISE}$			

2.6.9.5 System Controller Suspend Switching Characteristics

Table 87 • System Controller Suspend Entry and Exit Characteristics

Parameter	Symbol	Definition	Typ	Max	Unit
Time from TRSTb falling edge to SUSPEND_EN signal assertion	$T_{\text{suspend_Tr}}^{1,2}$	Suspend entry time from TRST_N assertion	1		μs
Time from TRSTb rising edge to ACTIVE signal assertion	$T_{\text{suspend_exit}}$	Suspend exit time from TRST_N negation	360		μs

1. ACTIVE indicates that the system controller is inactive or active regardless of the state of SUSPEND_EN.
2. ACTIVE signal must never be asserted with SUSPEND_EN is asserted.

2.6.9.6 Dynamic Reconfiguration Interface

The following table provides interface timing information for the DRI which is an embedded APB slave interface within the FPGA fabric that does not use FPGA resources.

Table 88 • Dynamic Reconfiguration Interface Timing Characteristics

Parameter	Symbol	Max	Unit
PCLK frequency	$F_{\text{PD_PCLK}}$	200	MHz

Figure 8 • Write Transfer Without Wait States

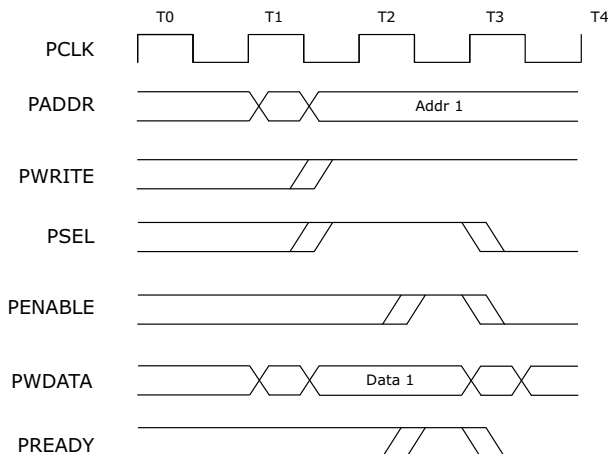
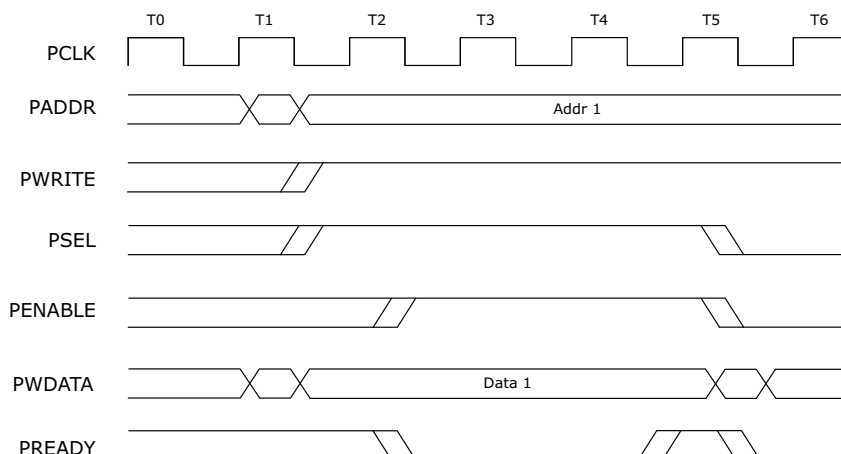
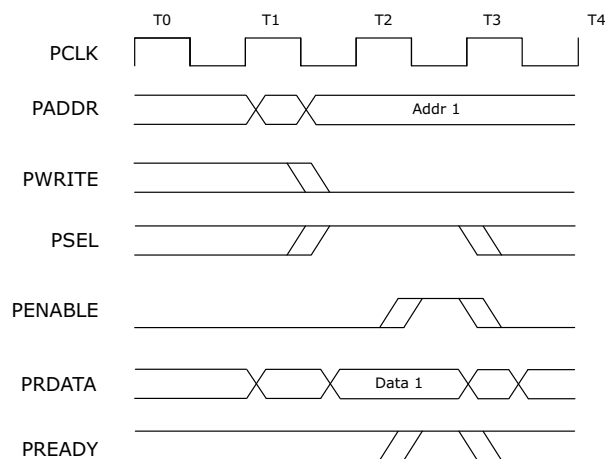
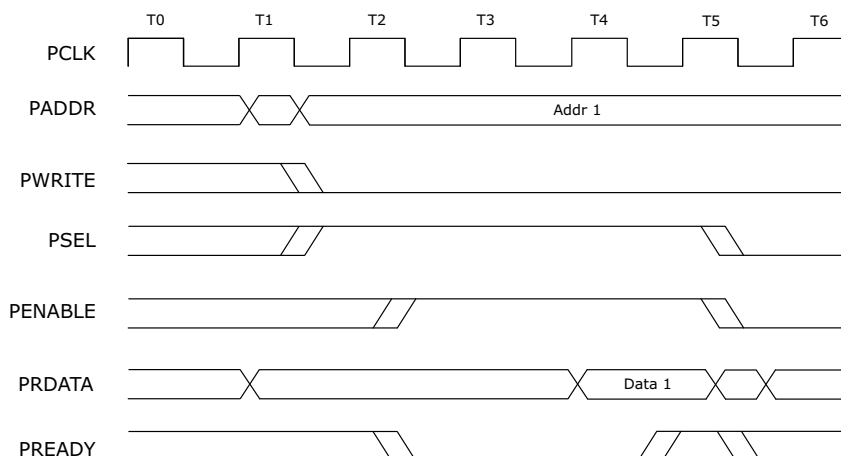


Figure 9 • Write Transfer With Wait States**Figure 10 • Read Transfer Without Wait States****Figure 11 • Read Transfer With Wait States**

2.6.10 Power-Up to Functional Timing

Microsemi non-volatile FPGA technology offers the fastest boot-time of any mid-range FPGA in the market. The following table describes both cold-boot (from Power-On) and warm-boot (assertion of DEVRST_N pin) timing. The power-up diagrams assume all power supplies to the device are stable.

Table 89 • Power-Up to Functional Timing

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Cold-Boot Power-Up to Functional Times						
Power-on reset circuit trip point	T _{POR_START}				μs	POR start = V _{DD} at 0.91 V, V _{DD18} at 1.6 V, V _{DDA} at 2.19 V
System controller start ¹	T _{BOOT_START} (COLD)		100		μs	
Warm-Boot Power-Up to Functional Times						
Warm reset	T _{WARM_RESET_START}					
The time from warm reset assertion to I/Os disabled	T _{IO_DISABLED}		1		μs	
DEVRST_N assertion time	T _{DEVRSTN}	1			μs	
Time from DEVRST_N negation to T _{BOOT} (WARM) if DEVRSTN asserted for less than 1000us			1000 - T _{DEVRSTN}		μs	
Time from DEVRST_N negation to T _{BOOT} (WARM) if DEVRSTN asserted for greater than 1000us			0		μs	
Cold and Warm Boot						
The time from T _{BOOT_START} to the FPGA Fabric operational	T _{FABRIC_UP}		550		μs	2 MHz and 160 MHz RC oscillators are available at this time
The time from FPGA fabric operational to FPGA inputs operational ²	T _{IN_ACTIVE}		25		μs	
The time from T _{BOOT_START} to FPGA fabric POR negation ²	T _{FAB_POR_DELAY}		600		μs	FABRIC_POR_N asserted to indicate to user design POR is complete
The time from T _{FAB_READY} to FPGA outputs operational ³	T _{OUT_ACTIVE}		200		μs	GPIO_ACTIVE and HSIO_ACTIVE indicate that I/O calibration is complete.
The time from T _{FAB_READY} to FPGA pull-up/pull-down operational	T _{PU_PD_ACTIVE}		200		μs	
IO bank controller calibration time period (HSIO/GPIO) assumes bank supplies are valid			200		μs	

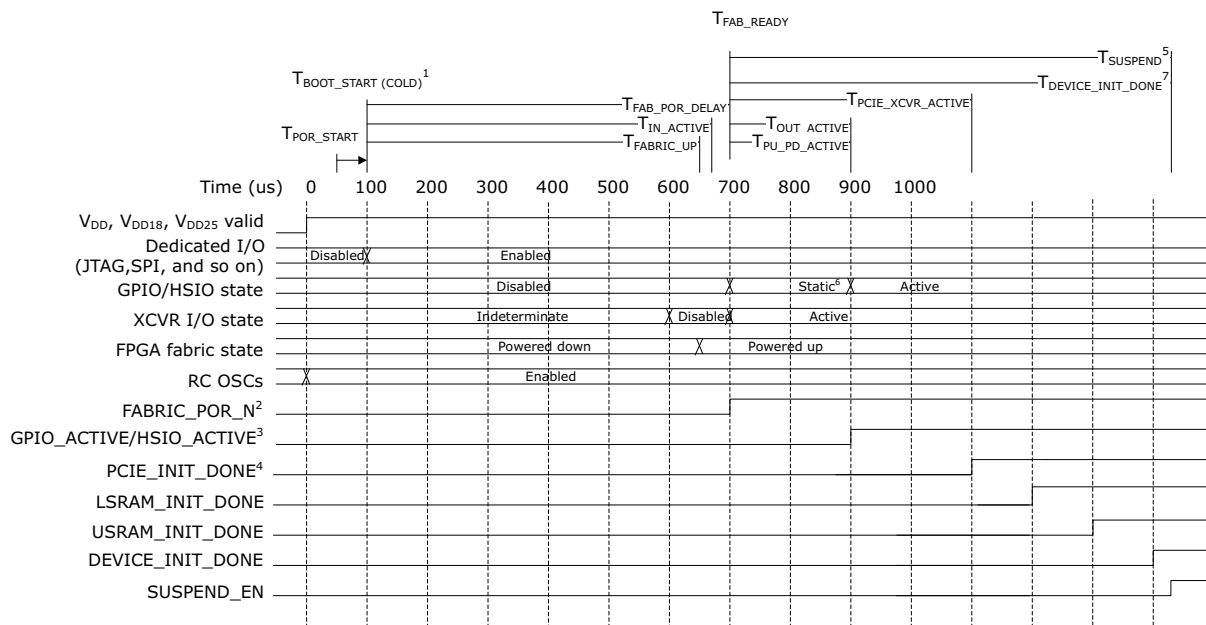
Table 89 • Power-Up to Functional Timing (continued)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
The time from T _{BOOT_START} to ready to program via JTAG/SPI-Slave			800		ms	
The time from T _{BOOT_START} to auto-update start			800		ms	
The time from T _{BOOT_START} to programming recovery start			800		ms	
The time from T _{FAB_READY} to transceivers PCIe initialization complete	T _{PCIE_XCVR_ACTIVE}				μs	
The time from T _{FAB_READY} to DEVICE_INIT_DONE assertion	T _{DEVICE_INIT_DONE}				ms	Dependent on the number of LSRAMs, μSRAMs, and Transceivers initialized
The time from DEVICE_INIT_DONE assertion to SUSPEND_EN signal assertion	T _{SUSPEND}		10		μs	
The time from T _{PORDELAY} to PLL/DLL initialization complete	T _{PLL_INIT}		200		μs	Valid at T _{FABRIC_UP}
The time from T _{FAB_READY} to PLL lock	T _{PLL_LOCK}		200			See Table 38, page 35
The time from T _{FAB_READY} to the PUF available for a system service call	T _{PUF_READY}		200		μs	Covered in System Service PUF dependent functions
The time from T _{FAB_READY} to the NRBG available (for S devices only)	T _{NRBG_READY}		200		μs	Covered in System Service PUF dependent functions
The time from T _{FAB_READY} to the tamper flags being available	T _{TAMPER_READY}		200		μs	Valid at T _{FABRIC_UP}
The time from T _{FAB_READY} to the Athena Crypto-co-processor being available (for S devices only)	T _{CRYPTO_READY}		200		μs	Valid at T _{FABRIC_UP}
Flash*Freeze						
The time from Flash*Freeze entry command to the Flash*Freeze state	T _{FF_ENTRY}		59		μs	
The time from Flash*Freeze exit pin assertion to fabric operational state	T _{FF_FABRIC_UP}		133		μs	
The time from Flash*Freeze exit pin assertion to I/Os operational	T _{FF_IO_ACTIVE}		143		μs	

1. V_{DDI3} and V_{DDAUX3} must be valid 50 usec before T_{BOOT_START} complete to avoid additional delay. V_{DDI3} = 0.85 V, V_{DDAUX3} = 1.6 V.
2. GPIO V_{DDIn} and V_{DDAUXn} must reach target 50 usec before T_{FABRIC_UP} to avoid delay. HSIO V_{DDIn} and V_{DD18} must reach target before T_{FABRIC_UP}. V_{DDIn} = 0.85 V, V_{DDAUXn} = 1.6 V, V_{DD18} = 1.6 V.
3. Inputs are ready 200 usec before T_{OUTPUT_ACTIVE}. I/Os can be configured to output a static state 1/0 before calibration is complete. Need to determined by user/Libero.

Note: Asserting reset from the tamper macro has the same power-up to functional timings starting from T_{BOOT_START} .

Figure 12 • Cold-Boot Power-Up to Functional Times



Note 1: System controller boots.

Note 2: Device initialization starts here. For PCIe, the termination value of XCVR I/O must be set to 50 Ω 70 ms before PVPRL after start of POR.

Note 3: For PCIe, PERST# or WAKE# must be operational before 50 ms after start of POR.

Note 4: For PCIe device configuration space must be accessible by host within 1 sec of negation of PERST#.

Note 5: SUSPEND_EN asserts only after cold boot and DEVICE_INIT_DONE asserts.

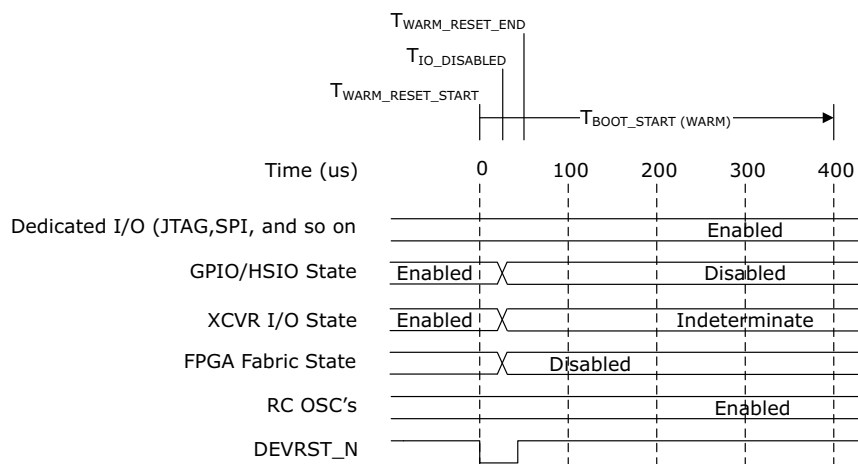
Note 6: I/O's can be configured to output a static state 1/0 before calibration is complete.

Note 7: User design dependent times dependent on the number of LSRAMs, uSRAMs, and transceivers initialized.

Note 8: Any delay in I/O supplies becoming valid will delay the I/O active times

Note 9: V_{DD13} and V_{DDAUX3} must be valid 50 usec before T_{BOOT_START} complete to avoid additional delay. $V_{DD13} = 0.85$ V, $V_{DDAUX3} = 1.6$ V.

Figure 13 • Warm-Boot Power-Up to Functional Times



Note: At time $T_{BOOT_START (WARM)}$, the FPGA boot process follows the cold start boot process at time $T_{BOOT_START (COLD)}$. For more information, see the preceding cold-boot power-up figure.

2.6.10.1 LSRAM and μ SRAM Initialization Time

Table 90 • Ram Initialization Characteristics

Parameter	Symbol	Typ	Max	Unit	Formula
INIT time of 1 LSRAM	T_{UPROM_LSRAM}				T1
INIT time of 1 μ SRAM	T_{UPROM_USRAM}				T2
INIT time of n LSRAM/LSRAMs in normal mode	$T_{UPROM_LSRAM_n}$				$n \times T1$
INIT time of n μ SRAM/ μ SRAM in normal mode	$T_{UPROM_USRAM_n}$				$n \times T2$
INIT time of n LSRAM in broadcast mode	$T_{UPROM_LSRAM_Br}$				T1
INIT time of n μ SRAM in broadcast mode	$T_{UPROM_USRAM_Br}$				T2
INIT time of 1 LSRAM	T_{SNVM_LSRAM}				T4
INIT time of 1 μ SRAM	T_{SNVM_USRAM}				T5
INIT time of n LSRAM/LSRAMs in normal mode	$T_{SNVM_LSRAM_n}$				$n \times T4$
INIT time of n μ SRAM/ μ SRAM in normal mode	$T_{SNVM_USRAM_n}$				$n \times T5$
INIT time of n LSRAM in broadcast mode	$T_{SNVM_LSRAM_Br}$				T4
INIT time of n μ SRAM in broadcast mode	$T_{SNVM_USRAM_Br}$				T5
INIT time of 1 LSRAM	$T_{SPI_PLAIN_LSRAM}$				T7
INIT time of 1 μ SRAM	$T_{SPI_PLAIN_USRAM}$				T8
INIT time of n LSRAMs in normal mode	$T_{SPI_PLAIN_LSRAM_n}$				$n \times T7$
INIT time of n μ SRAMs in normal mode	$T_{SPI_PLAIN_USRAM_n}$				$n \times T8$
INIT time of n LSRAM in broadcast mode	$T_{SPI_PLAIN_LSRAM_Br}$				T7
INIT time of n μ SRAM in broadcast mode	$T_{SPI_PLAIN_USRAM_Br}$				T8
INIT time of 1 LSRAM	$T_{SPI_AUTH_LSRAM}$				T10
INIT time of 1 μ SRAM	$T_{SPI_AUTH_USRAM}$				T11
INIT time of n LSRAMs in normal mode	$T_{SPI_AUTH_LSRAM_n}$				$n \times T10$
INIT time of n μ SRAMs in normal mode	$T_{SPI_AUTH_USRAM_n}$				$n \times T11$
INIT time of n LSRAM in broadcast mode	$T_{SPI_AUTH_LSRAM_Br}$				T10
INIT time of n μ SRAM in broadcast mode	$T_{SPI_AUTH_USRAM_Br}$				T11
INIT time of 1 LSRAM	$T_{SPI_ENCRYPT_LSRAM}$				T13
INIT time of 1 μ SRAM	$T_{SPI_ENCRYPT_USRAM}$				T14
INIT time of n LSRAMs in normal mode	$T_{SPI_ENCRYPT_LSRAM_n}$				$n \times T13$
INIT time of n μ SRAMs in normal mode	$T_{SPI_ENCRYPT_USRAM_n}$				$n \times T14$
INIT time of n LSRAM in broadcast mode	$T_{SPI_ENCRYPT_LSRAM_Br}$				T13
INIT time of n μ SRAM in broadcast mode	$T_{SPI_ENCRYPT_USRAM_Br}$				T14

2.6.11 Dedicated Pins

2.6.11.1 JTAG Switching Characteristics

Table 91 • JTAG Electrical Characteristics

Symbol	Description	Min	Typ	Max	Unit	Condition
T _{DISU}	TDI input setup time	0.0			ns	
T _{DIHD}	TDI input hold time			2.0	ns	
T _{TMSSU}	TMS input setup time	1.5			ns	
T _{TMSHD}	TMS input hold time			1.5	ns	
F _{TCK}	TCK frequency			25	MHz	
T _{TCKDC}	TCK duty cycle	40		60	%	
T _{TDOCQ}	TDO clock to Q out			7	ns	C _{LOAD} = 40 pf
T _{RSTBCQ}	TRSTB clock to Q out			23.5	ns	C _{LOAD} = 40 pf
T _{RSTBPW}	TRSTB min pulse width	50			ns	
T _{RSTBREM}	TRSTB removal time			0.0	ns	
T _{RSTBREC}	TRSTB recovery time	12.0			ns	
CIN _{TDI}	TDI input pin capacitance			5.3	pf	
CIN _{TMS}	TMS input pin capacitance			5.3	pf	
CIN _{TCK}	TCK input pin capacitance			5.3	pf	
CIN _{TRSTB}	TRSTB input pin capacitance			5.3	pf	

2.6.11.2 SPI Switching Characteristics

Table 92 • SPI Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SPI Master Mode (PolarFire Master) During Programming						
SCK frequency	F _{MSCK}			20	MHz	
SCK minimum clock period	T _{MSCKMP}	50			ns	
SCK minimum pulse width high	T _{MSCKPWH}	20			ns	
SCK minimum pulse width low	T _{MSCKPWL}	20			ns	
SDO clock to out	T _{SDOCO}			10	ns	
SDI setup time	T _{SDISU}	10			ns	
SDI hold time	T _{SDIHD}	10			ns	
SPI Master Mode (PolarFire Master) During Device Initialization						
SCK frequency	F _{MSCK}			40	MHz	
SCK minimum clock period	T _{MSCKMP}	25			ns	
SCK minimum pulse width high	T _{MSCKPWH}	10			ns	
SCK minimum pulse width low	T _{MSCKPWL}	10			ns	
SDO clock to out	T _{SDOCO}				ns	
SDI setup time	T _{SDISU}	5			ns	

Table 92 • SPI Electrical Characteristics (continued)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SDI hold time	T_{SDIHD}	5			ns	
SPI Slave Mode (PolarFire Slave)						
SCK frequency	F_{SSCK}			80	MHz	
SCK minimum clock period	T_{SSCKMP}	13			ns	
SCK minimum pulse width high	$T_{SSCKPWH}$	5			ns	
SCK minimum pulse width low	$T_{SSCKPWL}$	5			ns	
SDO clock to out	T_{SDOCO}			2.5	ns	
SDI setup time	T_{SDISU}	2.5			ns	
SDI hold time	T_{SDIHD}	2.5			ns	

2.6.11.3 SmartDebug Probe Switching Characteristics

Table 93 • SmartDebug Probe Performance Characteristics

Parameter	Symbol	$V_{DD} = 1.0\text{ V}$		$V_{DD} = 1.05\text{ V}$		Unit
		STD	-1	STD	-1	
Maximum frequency of probe signal	F_{MAX}	250	250	250	250	MHz
Minimum delay of probe signal	T_{Min_delay}	13	12	13	12	ns
Maximum delay of probe signal	T_{Max_delay}	13	12	13	12	ns

2.6.11.4 DEVRST_N Switching Characteristics

Table 94 • DEVRST_N Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
DEVRST_N ramp rate	DR_{RAMP}		10		us	It must be a normal clean digital signal, with typical rise and fall times.
Minimum DEVRST_N assert time	DR_{ASSERT}	1			us	The minimum time for DEVRST_N to be recognized
Minimum DEVRST_N de-assert time	$DR_{DEASSERT}$	1			us	The minimum time DEVRST_N needs to be de-asserted before assertion

2.6.11.5 FF_EXIT Switching Characteristics

Table 95 • FF_EXIT Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
FF_EXIT_N ramp rate	FF _{RAMP}		10		μs	
Minimum FF_EXIT_N assert time	FF _{ASSERT}		1		μs	The minimum time for FF_EXIT_N to be recognized
Minimum FF_EXIT_N de-assert time	FF _{DEASSERT}		1		μs	The minimum time FF_EXIT_N needs to be de-asserted before assertion

2.6.11.6 IO_CFG Switching Characteristics

Table 96 • IO_CFG Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
IO_CFG_N ramp rate	IOCFG _{RAMP}		10		μs	
Minimum IO_CFG_N assert time	IOCFG _{ASSERT}		1		μs	The minimum time for IO_CFG_N to be recognized
Minimum IO_CFG_N de-assert time	IOCFG _{DEASSERT}		1		μs	The minimum time IO_CFG_N needs to be de-asserted before assertion
IO_CFG_N to SPI Tristate	IOCFG _{TRISTATE}		20		ns	The time from IO_CFG_N changing to SPI pins going tri-state